GigaDevice Semiconductor Inc.

GD32F307xx Arm® Cortex®-M4 32-bit MCU

Datasheet

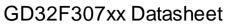


Table of Contents

Table	e of Contents	1
List	of Figures	4
List o	of Tables	5
1. 0	Seneral description	7
2. D	Device overview	8
2.1	. Device information	8
2.2	. Block diagram	9
2.3	. Pinouts and pin assignment	10
2.4	. Memory map	13
2.5		
2.6		
	.6.1. GD32F307Zx LQFP144 pin definitions	
2	.6.2. GD32F307Vx LQFP100 pin definitions	27
2	.6.3. GD32F307Rx LQFP64 pin definitions	34
3. F	unctional description	39
3.1	. Arm® Cortex®-M4 core	39
3.2	. On-chip memory	39
3.3	. Clock, reset and supply management	40
3.4	. Boot modes	40
3.5	. Power saving modes	41
3.6	. Analog to digital converter (ADC)	41
3.7	. Digital to analog converter (DAC)	42
3.8	. DM A	42
3.9	. General-purpose inputs/outputs (GPIOs)	42
3.1	0. Timers and PWM generation	43
3.1°	1. Real time clock (RTC)	44
3.1	2. Inter-integrated circuit (I2C)	44
3.1	3. Serial peripheral interface (SPI)	44
3.1	4. Universal synchronous asynchronous receiver transmitter (USART)	45
3.1	5. Inter-IC sound (I2S)	45



	3.16.	Universal serial bus full-speed interface (USBFS)	. 45
	3.17.	Controller area network (CAN)	. 46
	3.18.	Ethernet (ENET)	. 46
	3.19.	External memory controller (EXM C)	. 46
	3.20.	Debug mode	. 47
	3.21.	Package and operation temperature	. 47
4	. Ele	ctrical characteristics	. 48
	4.1.	Absolute maximum ratings	. 48
	4.2.	Operating conditions characteristics	. 48
	4.3.	Power consumption	. 50
	4.4.	EMC characteristics	. 57
	4.5.	Power supply supervisor characteristics	. 58
	4.6.	Electrical sensitivity	. 59
	4.7.	External clock characteristics	. 59
	4.8.	Internal clock characteristics	. 62
	4.9.	PLL characteristics	. 63
	4.10.	Memory characteristics	. 64
	4.11.	NRST pin characteristics	. 65
	4.12.	GPIO characteristics	. 66
	4.13.	Temperature sensor characteristics	. 67
	4.14.	ADC characteristics	. 67
	4.15.	DAC characteristics	. 69
	4.16.	I2C characteristics	. 70
	4.17.	SPI characteristics	. 71
	4.18.	I2S characteristics	. 72
	4.19.	USART characteristics	. 72
	4.20.	CAN characteristics	. 73
	4.21.	USBFS characteristics	. 73
	4.22.	EXMC characteristics	. 74
	4.23.	TIMER characteristics	. 78
	4.24.	WDGT characteristics	. 78
	4.25.	Parameter condition	. 78





5. Pa	ackage information	79
5.1.	LQFP144 package outline dimensions	79
5.2.	LQFP100 package outline dimensions	80
5.3.	LQFP64 package outline dimensions	82
6. Or	rdering information	83
7. Re	evision history	84



List of Figures

Figure 2-1 GD32F307xx block diagram	9
Figure 2-2 GD32F307Zx LQFP144 pinouts	10
Figure 2-3 GD32F307Vx LQFP100 pinouts	11
Figure 2-4 GD32F307Rx LQFP64 pinouts	12
Figure 2-5 GD32F307xx clock tree	17
Figure 4-1. Recommended power supply decoupling capacitors(1) (2)	48
Figure 4-2. Typical supply current consumption in Run mode	55
Figure 4-3. Typical supply current consumption in Sleep mode	56
Figure 4-4. Recommended external NRST pin circuit	65
Figure 4-5. I/O port AC characteristics definition	67
Figure 4-6. USBFS timings: definition of data signal rise and fall time	73
Figure 5-1. LQFP144 package outline	79
Figure 5-2. LQFP100 package outline	
Figure 5-3. LQFP64 package outline	



List of Tables

Table 2-1. GD32F307xx devices features and peripheral list	8
Table 2-2. GD32F307xx memory map	13
Table 2-3. GD32F307Zx LQFP144 pin definitions	18
Table 2-4. GD32F307Vx LQFP100 pin definitions	27
Table 2-5. GD32F307Rx LQFP64 pin definitions	34
Table 4-1. Absolute maximum ratings ^{(1) (4)}	48
Table 4-2. DC operating conditions	48
Table 4-3. Clock frequency ⁽¹⁾	49
Table 4-4. Operating conditions at Power up/ Power down ⁽¹⁾	
Table 4-5. Start-up timings of Operating conditions(1)(2)(3)	49
Table 4-6. Power saving mode wakeup timings characteristics ^{(1) (2)}	
Table 4-7. Power consumption characteristics (2)(3)(4)(5)	
Table 4-8. Peripheral current consumption characteristics ⁽¹⁾	56
Table 4-9. EMS characteristics ¹⁾	58
Table 4-10. Power supply supervisor characteristics	58
Table 4-11. ESD characteristics ⁽¹⁾	
Table 4-12. Static latch-up characteristics ⁽¹⁾	59
Table 4-13. High speed external clock (HXTAL) generated from a crystal/ceramic characteristics	.59
Table 4-14. High speed external clock characteristics (HXTAL in bypass mode)	60
Table 4-15. Low speed external clock (LXTAL) generated from a crystal/ceramic characteristics .	60
Table 4-16. Low speed external user clock characteristics (LXTAL in bypass mode)	61
Table 4-17. High speed internal clock (IRC8M) characteristics	
Table 4-18. Low speed internal clock (IRC40K) characteristics	62
Table 4-19. High speed internal clock (IRC48M) characteristics	
Table 4-20. PLL characteristics	
Table 4-21. PLL1 characteristics	
Table 4-22. PLL2 characteristics	
Table 4-23. Flash memory characteristics	64
Table 4-24. NRST pin characteristics	65
Table 4-25. I/O port DC characteristics ^{(1) (3)}	
Table 4-26. I/O port AC characteristics ⁽¹⁾⁽²⁾	
Table 4-27. Temperature sensor characteristics ⁽¹⁾	67
Table 4-28. ADC characteristics	67
Table 4-29. ADC R _{AIN max} for f _{ADC} = 40 MHz	
Table 4-30. ADC dynamic accuracy at f _{ADC} = 14 MHz ⁽¹⁾	
Table 4-31. ADC dynamic accuracy at $f_{ADC} = 40 \text{MHz}^{(1)}$	
Table 4-32. ADC static accuracy at f _{ADC} = 14 MHz ⁽¹⁾	
Table 4-33. DAC characteristics	
Table 4-34. I2C characteristics ⁽¹⁾⁽²⁾⁽³⁾	70
Table 4-35. Standard SPI characteristics ⁽¹⁾	

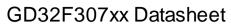




Table 4-36. I2S characteristics ^{(1) (2)}	72
Table 4-37. USART characteristics ⁽¹⁾	72
Table 4-38. USBFS start up time	73
Table 4-39. USBFS DC electrical characteristics	73
Table 4-40. USBFS full speed-electrical characteristics (1)	73
Table 4-41. A synchronous non-multiplexed SRAM/PSRAM/NOR read timings (1)(2)(3)(4)	74
Table 4-42. A synchronous non-multiplexed SRAM/PSRAM/NOR write timings (1)(2)(3)(4)	74
Table 4-43. A synchronous multiplexed PSRAM/NOR read timings (1)(2)(3)(4)	75
Table 4-44. A synchronous multiplexed PSRAM/NOR write timings (1)(2)(3)(4)	75
Table 4-45. Synchronous multiplexed PSRAM/NOR read timings (1)(2)(3)(4)	76
Table 4-46. Synchronous multiplexed PSRAM write timings (1)(2)(3)(4)	76
Table 4-47. Synchronous non-multiplexed PSRAM/NOR read timings (1)(2)(3)(4)	77
Table 4-48. Synchronous non-multiplexed PSRAM write timings (1)(2)(3)(4)	77
Table 4-49. TIMER characteristics (1)	78
Table 4-50. FWDGT min/max timeout period at 40 kHz (IRC40K) ⁽¹⁾	78
Table 4-51. WWDGT min-max timeout value at 60 MHz (f _{PCLK1}) ⁽¹⁾	78
Table 5-1. LQFP144 package dimensions	79
Table 5-2. LQFP100 package dimensions	80
Table 5-3. LQFP64 package dimensions	82
Table 6-1. Part ordering code for GD32F307xx devices	83
Table 7-1. Revision history	84



1. General description

The GD32F307xx device belongs to the mainstream line of GD32 MCU Family. It is a new 32-bit general-purpose microcontroller based on the Arm® Cortex®-M4 RISC core with best cost-performance ratio in terms of enhanced processing capacity, reduced power consumption and peripheral set. The Cortex®-M4 core features implements a full set of DSP instructions to address digital signal control markets that demand an efficient, easy-to-use blend of control and signal processing capabilities. It also provides a Memory Protection Unit (MPU) and powerful trace technology for enhanced application security and advanced debug support.

The GD32F307xx device incorporates the Arm® Cortex®-M4 32-bit processor core operating at 120 MHz frequency with Flash accesses zero wait states to obtain maximum efficiency. It provides up to 1024 KB on-chip Flash memory and 96 KB SRAM memory. An extensive range of enhanced I/Os and peripherals connected to two APB buses. The devices offer up to two 12-bit 2.6 MSPS ADCs, two 12-bit DACs, up to ten general 16-bit timers, two 16-bit PWM advanced timers, and two 16-bit basic timers, as well as standard and advanced communication interfaces: up to three SPIs, two I2Cs, three USARTs and two UARTs, two I2Ss, two CANs, a USBFS and an ENET.

The device operates from a 2.6 to 3.6 V power supply and available in -40 to +85 °C temperature range. Several power saving modes provide the flexibility for maximum optimization between wakeup latency and power consumption, an especially important consideration in low power applications.

The above features make GD32F307xx devices suitable for a wide range of interconnection and advanced applications, especially in areas such as industrial control, consumer and handheld equipment, communication networks, embedded modules, human machine interface, security and alarm systems, graphic display, automotive navigation, IoT and so on.





2. Device overview

2.1. Device information

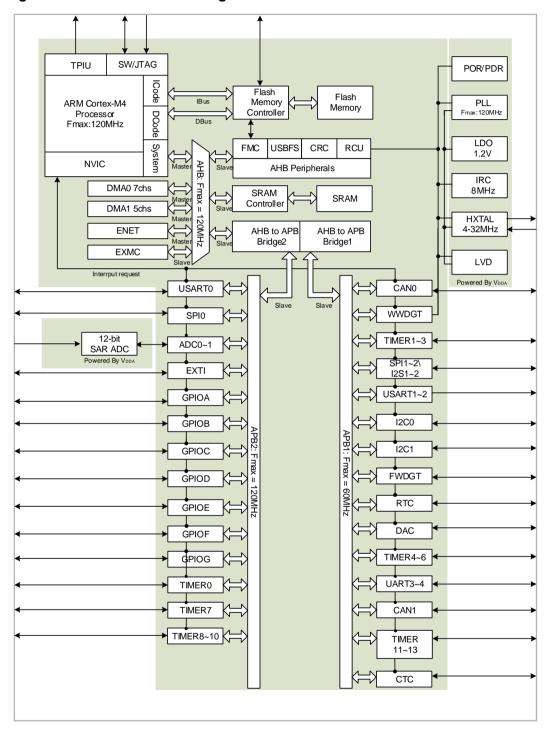
Table 2-1. GD32F307xx devices features and peripheral list

	ble 2-1. GD32	GD32F307xx								
	Part Number	RC	RE	RG	vc	VE	VG	zc	ZE	ZG
	Code area (KB)	256	256	256	256	256	256	256	256	256
Flash	Data area (KB)	0	256	768	0	256	768	0	256	768
	Total (KB)	256	512	1024	256	512	1024	256	512	1024
	SRAM (KB)	96	96	96	96	96	96	96	96	96
	General	4	4	10	4	4	10	4	4	10
	timer(16-bit)	(1-4)	(1-4)	(1-4,8-13)	(1-4)	(1-4)	(1-4,8-13)	(1-4)	(1-4)	(1-4,8-13)
	Advanced	1	2	2	1	2	2	2	2	2
v	timer(16-bit)	(0)	(0,7)	(0,7)	(0)	(0,7)	(0,7)	(0,7)	(0,7)	(0,7)
Timers	Basic	2	2	2	2	2	2	2	2	2
Ħ	timer(16-bit)	(5-6)	(5-6)	(5-6)	(5-6)	(5-6)	(5-6)	(5-6)	(5-6)	(5-6)
	SysTick	1	1	1	1	1	1	1	1	1
	Watchdog	2	2	2	2	2	2	2	2	2
	RTC	1	1	1	1	1	1	1	1	1
	USART	3	3	3	3	3	3	3	3	3
		(0-2)	(0-2)	(0-2)	(0-2)	(0-2)	(0-2)	(0-2)	(0-2)	(0-2)
	UART	2	2	2	2	2	2	2	2	2
2		(3-4)	(3-4)	(3-4)	(3-4)	(3-4)	(3-4)	(3-4)	(3-4)	(3-4)
ctivi	I2C	2	2	2	2	2	2	2	2	2
Connectivity	SPI/I2S	3/2	3/2	3/2	3/2	3/2	3/2	3/2	3/2	3/2
CO	01 1/120	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)
	ENET	1	1	1	1	1	1	1	1	1
	CAN	2	2	2	2	2	2	2	2	2
	USBFS	1	1	1	1	1	1	1	1	1
	GPIO	51	51	51	80	80	80	112	112	112
	EXMC	0	0	0	1	1	1	1	1	1
	EXTI	16	16	16	16	16	16	16	16	16
Α	DC Unit (CHs)	2(16)	2(16)	2(16)	2(16)	2(16)	2(16)	2(16)	2(16)	2(16)
	DAC	2	2	2	2	2	2	2	2	2
	Package		LQFP64			LQFP100			LQFP144	



2.2. Block diagram

Figure 2-1 GD32F307xx block diagram





2.3. Pinouts and pin assignment

Figure 2-2 GD32F307Zx LQFP144 pinouts

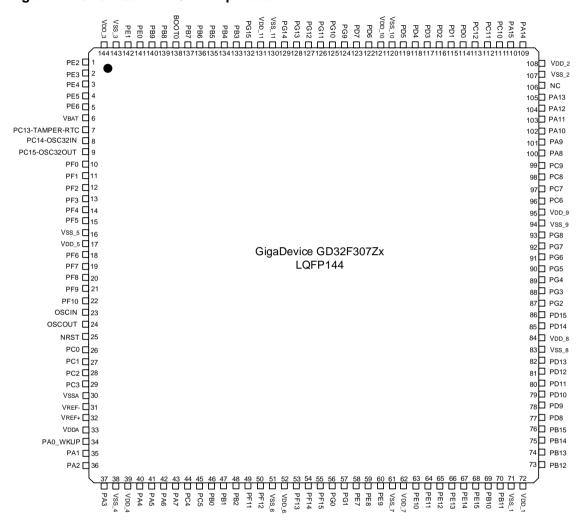




Figure 2-3 GD32F307Vx LQFP100 pinouts

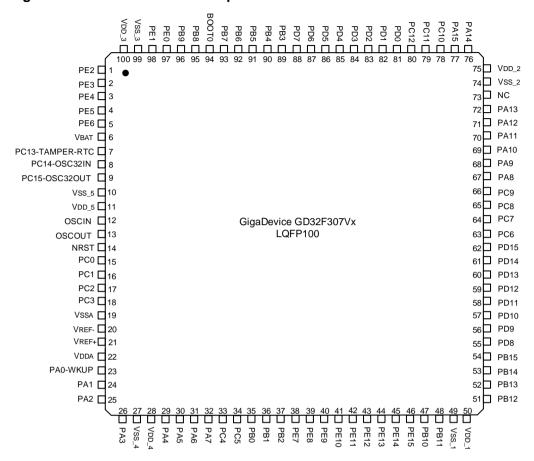
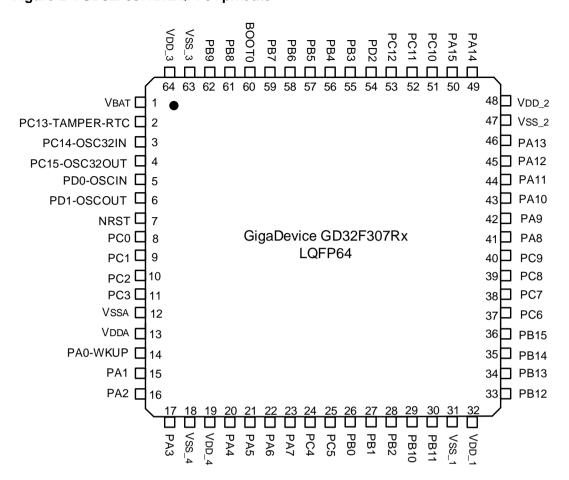




Figure 2-4 GD32F307Rx LQFP64 pinouts

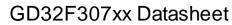




2.4. Memory map

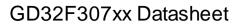
Table 2-2. GD32F307xx memory map

Pre-defined		memory map	De whole a sele		
Regions	Bus	Address	Peripherals		
External device		0xA000 0000 - 0xA000 0FFF	EXMC - SWREG		
	ALIDO	0x9000 0000 - 0x9FFF FFFF	EXMC - PC CARD		
External RAM	AHB3	0x7000 0000 - 0x8FFF FFFF	EXMC - NAND		
		0x6000 0000 - 0x6FFF FFFF	EXMC - NOR/PSRA M/SRA M		
		0x5000 0000 - 0x5003 FFFF	USBFS		
		0x4008 0000 - 0x4FFF FFFF	Reserved		
		0x4004 0000 - 0x4007 FFFF	Reserved		
		0x4002 BC00 - 0x4003 FFFF	Reserved		
		0x4002 B000 - 0x4002 BBFF	Reserved		
		0x4002 A000 - 0x4002 AFFF	Reserved		
		0x4002 8000 - 0x4002 9FFF	ENET		
		0x4002 6800 - 0x4002 7FFF	Reserved		
		0x4002 6400 - 0x4002 67FF	Reserved		
		0x4002 6000 - 0x4002 63FF	Reserved		
		0x4002 5000 - 0x4002 5FFF	Reserved		
	AHB1	0x4002 4000 - 0x4002 4FFF	Reserved		
		0x4002 3C00 - 0x4002 3FFF	Reserved		
		0x4002 3800 - 0x4002 3BFF	Reserved		
		0x4002 3400 - 0x4002 37FF	Reserved		
		0x4002 3000 - 0x4002 33FF	CRC		
Peripheral		0x4002 2C00 - 0x4002 2FFF	Reserved		
		0x4002 2800 - 0x4002 2BFF	Reserved		
		0x4002 2400 - 0x4002 27FF	Reserved		
		0x4002 2000 - 0x4002 23FF	FMC		
		0x4002 1C00 - 0x4002 1FFF	Reserved		
		0x4002 1800 - 0x4002 1BFF	Reserved		
		0x4002 1400 - 0x4002 17FF	Reserved		
		0x4002 1000 - 0x4002 13FF	RCU		
		0x4002 0C00 - 0x4002 0FFF	Reserved		
		0x4002 0800 - 0x4002 0BFF	Reserved		
		0x4002 0400 - 0x4002 07FF	DMA1		
		0x4002 0000 - 0x4002 03FF	DMA0		
		0x4001 8400 - 0x4001 FFFF	Reserved		
		0x4001 8000 - 0x4001 83FF	Reserved		
		0x4001 7C00 - 0x4001 7FFF	Reserved		
	APB2	0x4001 7800 - 0x4001 7BFF	Reserved		
		0x4001 7400 - 0x4001 77FF	Reserved		





Pre-defined Bus		Address	Peripherals
Regions		0x4001 7000 - 0x4001 73FF	Reserved
		0x4001 6C00 - 0x4001 6FFF	Reserved
		0x4001 6800 - 0x4001 6BFF	Reserved
		0x4001 5C00 - 0x4001 67FF	Reserved
		0x4001 5800 - 0x4001 5BFF	Reserved
		0x4001 5400 - 0x4001 57FF	TIMER10
		0x4001 5000 - 0x4001 53FF	TIMER9
		0x4001 4C00 - 0x4001 4FFF	TIMER8
		0x4001 4800 - 0x4001 4BFF	Reserved
		0x4001 4400 - 0x4001 47FF	Reserved
		0x4001 4000 - 0x4001 43FF	Reserved
		0x4001 3C00 - 0x4001 3FFF	Reserved
		0x4001 3800 - 0x4001 3BFF	USART0
		0x4001 3400 - 0x4001 37FF	TIMER7
		0x4001 3000 - 0x4001 33FF	SPI0
		0x4001 2C00 - 0x4001 2FFF	TIMER0
		0x4001 2800 - 0x4001 2BFF	ADC1
		0x4001 2400 - 0x4001 27FF	ADC0
		0x4001 2000 - 0x4001 23FF	GPIOG
		0x4001 1C00 - 0x4001 1FFF	GPIOF
		0x4001 1800 - 0x4001 1BFF	GPIOE
		0x4001 1400 - 0x4001 17FF	GPIOD
		0x4001 1000 - 0x4001 13FF	GPIOC
		0x4001 0C00 - 0x4001 0FFF	GPIOB
		0x4001 0800 - 0x4001 0BFF	GPIOA
		0x4001 0400 - 0x4001 07FF	EXTI
		0x4001 0000 - 0x4001 03FF	AFIO
		0x4000 CC00 - 0x4000 FFFF	Reserved
		0x4000 C800 - 0x4000 CBFF	СТС
		0x4000 C400 - 0x4000 C7FF	Reserved
		0x4000 C000 - 0x4000 C3FF	Reserved
		0x4000 8000 - 0x4000 BFFF	Reserved
		0x4000 7C00 - 0x4000 7FFF	Reserved
	APB1	0x4000 7800 - 0x4000 7BFF	Reserved
	W DI	0x4000 7400 - 0x4000 7BFF	DAC
		0x4000 7400 - 0x4000 7711	PMU
		0x4000 7000 - 0x4000 75FF 0x4000 6C00 - 0x4000 6FFF	BKP
			CAN1
		0x4000 6800 - 0x4000 6BFF	
		0x4000 6400 - 0x4000 67FF	CANO CAN STAN STAN INVEST.
		0x4000 6000 - 0x4000 63FF	CAN SRAM 512 bytes





Pre-defined	Bue	Address	Davimhavela
Regions	Bus	Address	Peripherals
		0x4000 5C00 - 0x4000 5FFF	Reserved
		0x4000 5800 - 0x4000 5BFF	I2C1
		0x4000 5400 - 0x4000 57FF	I2C0
		0x4000 5000 - 0x4000 53FF	UART4
		0x4000 4C00 - 0x4000 4FFF	UART3
		0x4000 4800 - 0x4000 4BFF	USART2
		0x4000 4400 - 0x4000 47FF	USART1
		0x4000 4000 - 0x4000 43FF	Reserved
		0x4000 3C00 - 0x4000 3FFF	SPI2/I2S2
		0x4000 3800 - 0x4000 3BFF	SP11/I2S1
		0x4000 3400 - 0x4000 37FF	Reserved
		0x4000 3000 - 0x4000 33FF	FWDGT
		0x4000 2C00 - 0x4000 2FFF	WWDGT
		0x4000 2800 - 0x4000 2BFF	RTC
		0x4000 2400 - 0x4000 27FF	Reserved
		0x4000 2000 - 0x4000 23FF	TIMER13
		0x4000 1C00 - 0x4000 1FFF	TIMER12
		0x4000 1800 - 0x4000 1BFF	TIMER11
		0x4000 1400 - 0x4000 17FF	TIMER6
		0x4000 1000 - 0x4000 13FF	TIMER5
		0x4000 0C00 - 0x4000 0FFF	TIMER4
		0x4000 0800 - 0x4000 0BFF	TIMER3
		0x4000 0400 - 0x4000 07FF	TIMER2
		0x4000 0000 - 0x4000 03FF	TIMER1
		0x2007 0000 - 0x3FFF FFFF	Reserved
		0x2006 0000 - 0x2006 FFFF	Reserved
SRAM	AHB	0x2003 0000 - 0x2005 FFFF	Reserved
		0x2001 8000 - 0x2002 FFFF	Reserved
		0x2000 0000 - 0x2001 7FFF	SRAM
		0x1FFF F810 - 0x1FFF FFFF	Reserved
		0x1FFF F800 - 0x1FFF F80F	Option Bytes
		0x1FFF F000 - 0x1FFF F7FF	
		0x1FFF C010 - 0x1FFF EFFF	D 44
		0x1FFF C000 - 0x1FFF C00F	Boot loader
Code	AHB	0x1FFF B000 - 0x1FFF BFFF	
		0x1FFF 7A10 - 0x1FFF AFFF	Reserved
		0x1FFF 7800 - 0x1FFF 7A0F	Reserved
		0x1FFF 0000 - 0x1FFF 77FF	Reserved
		0x1FFE C010 - 0x1FFE FFFF	Reserved
		0x1FFE C000 - 0x1FFE C00F	Reserved



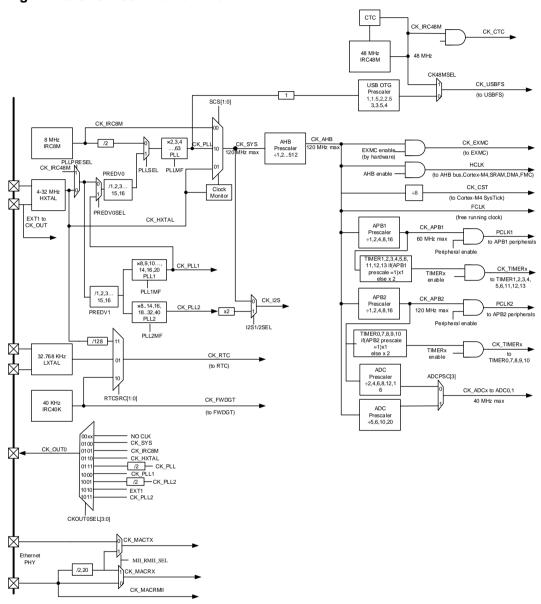
GD32F307xx Datasheet

Pre-defined Regions	Bus	Address	Peripherals
		0x1001 0000 - 0x1FFE BFFF	Reserved
		0x1000 0000 - 0x1000 FFFF	Reserved
		0x083C 0000 - 0x0FFF FFFF	Reserved
		0x0830 0000 - 0x083B FFFF	Reserved
		0x0810 0000 - 0x082F FFFF	Reserved
		0x0800 0000 - 0x080F FFFF	Main Flash
		0x0030 0000 - 0x07FF FFFF	Reserved
		0x0010 0000 - 0x002F FFFF	Alice and to Main Fleeh or Rest
		0x0002 0000 - 0x000F FFFF	Aliased to Main Flash or Boot loader
		0x0000 0000 - 0x0001 FFFF	ioauei



2.5. Clock tree

Figure 2-5 GD32F307xx clock tree



Legend:

HXTAL: High speed crystal oscillator LXTAL: Low speed crystal oscillator IRC8M: Internal 8M RC oscillators IRC40K: Internal 40K RC oscillator IRC48M: Internal 48M RC oscillators



2.6. Pin definitions

2.6.1. GD32F307Zx LQFP144 pin definitions

Table 2-3. GD32F307Zx LQFP144 pin definitions

Table 2-3. GD32F30/ZX LQFP144 pin definitions					
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description	
PE2	1	VO	5VT	Default: PE2 Alternate: TRACECK, EXMC_A23	
PE3	2	VO	5VT	Default: PE3 Alternate: TRACED0, EXMC_A19	
PE4	3	VO	5VT	Default: PE4 Alternate:TRACED1, EXMC_A20	
PE5	4	VO	5VT	Default: PE5 Alternate:TRACED2, EXMC_A21 Remap: TIMER8_CH0 ⁽³⁾	
PE6	5	VO	5VT	Default: PE6 Alternate:TRACED3, EXMC_A22 Remap: TIMER8_CH1 ⁽³⁾	
V _{BAT}	6	Р		Default: V _{BAT}	
PC13- TAMPER- RTC	7	VO		Default: PC13 Alternate: TAMPER-RTC	
PC14- OSC32IN	8	VO		Default: PC14 Alternate: OSC32IN	
PC15- OSC32OUT	9	VO		Default: PC15 Alternate: OSC32OUT	
PF0	10	VO	5VT	Default: PF0 Alternate: EXMC_A0 Remap: CTC_SYNC	
PF1	11	VO	5VT	Default: PF1 Alternate: EXMC_A1	
PF2	12	VO	5VT	Default: PF2 Alternate: EXMC_A2	
PF3	13	VO	5VT	Default: PF3 Alternate: EXMC_A3	
PF4	14	VO	5VT	Default: PF4 Alternate: EXMC_A4	
PF5	15	VO	5VT	Default: PF5 Alternate: EXMC_A5	
V _{SS_5}	16	Р		Default: V _{SS_5}	
V _{DD_5}	17	Р		Default: V _{DD_5}	



Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				Default: PF6
PF6	18	VO		Alternate: EXMC_NIORD
				Remap: TIMER9_CH0 Default: PF7
PF7	19	VO		Alternate: EXMC_NREG
1.7	10	••		Remap: TIMER10_CH0 ⁽³⁾
				Default: PF8
PF8	20	VO		Alternate: EXMC_NIOWR
				Remap: TIMER12_CH0 ⁽³⁾
				Default: PF9
PF9	21	VO		Alternate: EXMC_CD
				Remap: TIMER13_CH0 ⁽³⁾
PF10	22	VO		Default: PF10 Alternate: EXMC_INTR
				Default: OSCIN
OSCIN	23	I		Remap: PD0
				Default: OSCOUT
OSCOUT	24	0		Remap: PD1
NRST	25	VO		Default: NRST
DCO	26	VO		Default: PC0
PC0	26	10		Alternate: ADC01_IN10
PC1	27	VO		Default: PC1
				Alternate: ADC01_IN11, ENET_MDC
PC2	28	VO		Default: PC2
				Alternate: ADC01_IN12, ENET_MII_TXD2 Default: PC3
PC3	29	VO		Alternate: ADC01_IN13, ENET_MII_TX_CLK
V _{SSA}	30	Р		Default: V _{SSA}
V _{REF-}	31	Р		Default: V _{REF} -
V _{REF+}	32	Р		Default: V _{REF+}
V _{DDA}	33	Р		Default: V _{DDA}
PA0-WKUP	34	VO		Default: PA0 Alternate: WKUP, USART1_CTS, ADC01_IN0, TIMER1_CH0, TIMER1_ETI, TIMER4_CH0, TIMER7_ETI, ENET_MII_CRS
PA1	35	VO		Default: PA1 Alternate: USART1_RTS, ADC01_IN1, TIMER1_CH1, TIMER4_CH1, ENET_MII_RX_CLK, ENET_RMII_REF_CLK
PA2	36	VO		Default: PA2 Alternate: USART1_TX, ADC01_IN2, TIMER1_CH2, TIMER4_CH2, TIMER8_CH0 ⁽³⁾ , ENET_MDIO,



				ODOZI OO7 XX DataSHCC
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				SPI0_IO2
PA3	37	VO		Default: PA3 Alternate: USART1_RX, ADC01_IN3, TIMER1_CH3, TIMER4_CH3, TIMER8_CH1 ⁽³⁾ , ENET_MII_COL, SPI0_IO3
V _{SS_4}	38	Р		Default: V _{SS_4}
V_{DD_4}	39	Р		Default: V _{DD_4}
PA4	40	VO		Default: PA4 Alternate: SPI0_NSS, USART1_CK, ADC01_IN4, DAC_OUT0 Remap:SPI2_NSS, I2S2_WS
PA5	41	VO		Default: PA5 Alternate: SPI0_SCK, ADC01_IN5, DAC_OUT1
PA6	42	VO		Default: PA6 Alternate: SPI0_MISO, ADC01_IN6, TIMER2_CH0, TIMER7_BRKIN, TIMER12_CH0 ⁽³⁾ Remap: TIMER0_BRKIN
PA7	43	VO		Default: PA7 Alternate: SPI0_MOSI, ADC01_IN7, TIMER2_CH1, TIMER7_CH0_ON, TIMER13_CH0 ⁽³⁾ , ENET_MII_RX_DV, ENET_RMII_CRS_DV Remap: TIMER0_CH0_ON
PC4	44	VO		Default: PC4 Alternate: ADC01_IN14, ENET_MII_RXD0, ENET_RMII_RXD0
PC5	45	VO		Default: PC5 Alternate: ADC01_IN15, ENET_MII_RXD1, ENET_RMII_RXD1
PB0	46	VO		Default: PB0 Alternate: ADC01_IN8, TIMER2_CH2, TIMER7_CH1_ON, ENET_MII_RXD2 Remap: TIMER0_CH1_ON
PB1	47	VO		Default: PB1 Alternate: ADC01_IN9, TIMER2_CH3, TIMER7_CH2_ON, ENET_MII_RXD3 Remap: TIMER0_CH2_ON
PB2	48	VO	5VT	Default: PB2, BOOT1
PF11	49	VO	5VT	Default: PF11 Alternate: EXMC_NIOS16
PF12	50	VO	5VT	Default: PF12 Alternate: EXMC_A6
V _{SS_6}	51	Р		Default: V _{SS 6}
-				



				GD321 307 XX DataStilee
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
V_{DD_6}	52	Р		Default: V _{DD_6}
				Default: PF13
PF13	53	VO	5VT	Alternate: EXMC_A7
PF14	54	VO	5VT	Default: PF14 Alternate: EXMC_A8
PF15	55	VO	5VT	Default: PF15 Alternate: EXMC_A9
PG0	56	VO	5VT	Default: PG0 Alternate: EXMC_A10
PG1	57	VO	5VT	Default: PG1 Alternate: EXMC_A11
PE7	58	VO	5VT	Default: PE7 Alternate: EXMC_D4 Remap: TIMER0_ETI
PE8	59	ľO	5VT	Default: PE8 Alternate: EXMC_D5 Remap: TIMER0_CH0_ON
PE9	60	VO	5VT	Default: PE9 Alternate: EXMC_D6 Remap: TIMER0_CH0
V _{SS_7}	61	Р		Default: V _{SS_7}
V _{DD 7}	62	Р		Default: V _{DD_7}
PE10	63	VO	5VT	Default: PE10 Alternate: EXMC_D7 Remap: TIMER0_CH1_ON
PE11	64	VO	5VT	Default: PE11 Alternate: EXMC_D8 Remap: TIMER0_CH1
PE12	65	VO	5VT	Default: PE12 Alternate: EXMC_D9 Remap: TIMER0_CH2_ON
PE13	66	VO	5VT	Default: PE13 Alternate: EXMC_D10 Remap: TIMER0_CH2
PE14	67	VO	5VT	Default: PE14 Alternate: EXMC_D11 Remap: TIMER0_CH3
PE15	68	VO	5VT	Default: PE15 Alternate: EXMC_D12 Remap: TIMER0_BRKIN
PB10	69	VO	5VT	Default: PB10 Alternate: I2C1_SCL, USART2_TX, ENET_MII_RX_ER



				ODOZI 307 XX Dalastice
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				Remap: TIMER1_CH2
PB11	70	VO	5VT	Default: PB11 Alternate: I2C1_SDA, USART2_RX, ENET_MII_TX_EN, ENET_RMII_TX_EN Remap: TIMER1_CH3
V _{SS_1}	71	Р		Default: V _{SS_1}
V_{DD_1}	72	Р		Default: V _{DD_1}
PB12	73	VO	5VT	Default: PB12 Alternate: SP11_NSS, I2C1_SMBA, USART2_CK, TIMER0_BRKIN, I2S1_WS, CAN1_RX, ENET_MII_TXD0, ENET_RMII_TXD0
PB13	74	VO	5VT	Default: PB13 Alternate: SP1_SCK, USART2_CTS, TIMER0_CH0_ON, I2S1_CK, CAN1_TX, ENET_MII_TXD1, ENET_RMII_TXD1
PB14	75	VO	5VT	Default: PB14 Alternate: SP1_MISO, USART2_RTS, TIMER0_CH1_ON, TIMER11_CH0 ⁽³⁾
PB15	76	VO	5VT	Default: PB15 Alternate: SP1_MOSI, TIMER0_CH2_ON, I2S1_SD, TIMER11_CH1 ⁽³⁾
PD8	77	VO	5VT	Default: PD8 Alternate: EXMC_D13 Remap: USART2_TX, ENET_MII_RX_DV, ENET_RMII_CRS_DV
PD9	78	VO	5VT	Default: PD9 Alternate: EXMC_D14 Remap: USART2_RX, ENET_MII_RXD0, ENET_RMII_RXD0
PD10	79	VO	5VT	Default: PD10 Alternate: EXMC_D15 Remap: USART2_CK, ENET_MII_RXD1, ENET_RMII_RXD1
PD11	80	VO	5VT	Default: PD11 Alternate: EXMC_A16 Remap: USART2_CTS, ENET_MII_RXD2
PD12	81	VO	5VT	Default: PD12 Alternate: EXMC_A17 Remap: TIMER3_CH0, USART2_RTS, ENET_MIL_RXD3
PD13	82	VO	5VT	Default: PD13 Alternate: EXMC_A18 Remap: TIMER3_CH1



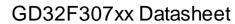
F	Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
	V _{SS_8}	83	Р		Default: V _{SS_8}
	V _{DD_8}	84	Р		Default: V _{DD 8}
	PD14	85	VO	5VT	Default: PD14 Alternate: EXMC_D0 Remap: TIMER3_CH2
	PD15	86	VO	5VT	Default: PD15 Alternate: EXMC_D1 Remap: TIMER3_CH3, CTC_SYNC
	PG2	87	VO	5VT	Default: PG2 Alternate: EXMC_A12
	PG3	88	VO	5VT	Default: PG3 Alternate: EXMC_A13
	PG4	89	VO	5VT	Default: PG4 Alternate: EXMC_A14
	PG5	90	VO	5VT	Default: PG5 Alternate: EXMC_A15
	PG6	91	VO	5VT	Default: PG6 Alternate: EXMC_INT1
	PG7	92	VO	5VT	Default: PG7 Alternate: EXMC_INT2
	PG8	93	VO	5VT	Default: PG8
	V _{SS_9}	94	Р		Default: V _{SS_9}
	V_{DD_9}	95	Р		Default: V _{DD_9}
	PC6	96	VO	5VT	Default: PC6 Alternate: I2S1_MCK, TIMER7_CH0 Remap: TIMER2_CH0
	PC7	97	VO	5VT	Default: PC7 Alternate: I2S2_MCK, TIMER7_CH1 Remap: TIMER2_CH1
	PC8	98	VO	5VT	Default: PC8 Alternate: TIMER7_CH2 Remap: TIMER2_CH2
	PC9	99	VO	5VT	Default: PC9 Alternate: TIMER7_CH3 Remap: TIMER2_CH3
	PA8	100	VO	5VT	Default: PA8 Alternate: USART0_CK, TIMER0_CH0, CK_OUT0, USBFS_SOF, CTC_SYNC
	PA9	101	VO	5VT	Default: PA9 Alternate: USART0_TX, TIMER0_CH1, USBFS_VBUS
	PA10	102	VO	5VT	Default: PA10



				ODSZI SOTAX Datastice
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				Alternate: USARTO_RX, TIMERO_CH2, USBFS_ID
				Default: PA11
PA11	103	VO	5VT	Alternate: USARTO_CTS, CANO_RX, USBFS_DM, TIMERO_CH3
PA12	104	VO	5VT	Default: PA12 Alternate: USART0_RTS, USBFS_DP, CAN0_TX, TIMER0 ETI
PA13	105	VO	5VT	Default: JTMS, SWDIO Remap: PA13
NC	106	-	-	-
V _{SS_2}	107	Р		Default: V _{SS 2}
V _{DD_2}	108	P		Default: V _{DD 2}
V DD_2	100	F		Default: JTCK, SWCLK
PA14	109	VO	5VT	Remap: PA14
				·
				Default: JTDI Alternate: SPI2_NSS, I2S2_WS
PA 15	110	VO	5VT	i e
				Remap: TIMER1_CH0, TIMER1_ETI, PA15, SPI0_NSS
				Default: PC10
PC10	111	VO	5VT	Alternate: UART3_TX
PCIO	'''	10	371	Remap: USART2_TX, SPI2_SCK, I2S2_CK
				Default: PC11
PC11	112	VO	5VT	Alternate: UART3_RX
FOIT	112	V O	3 1	Remap: USART2_RX, SPI2_MISO
				Default: PC12
PC12	113	VO	5VT	Alternate: UART4_TX
FCIZ	113	10	371	Remap: USART2_CK, SPI2_MOSI, I2S2_SD
				Default: PD0
PD0	114	VO	5VT	Alternate: EXMC_D2
120	''-	,,	371	Remap: CAN0_RX, OSCIN
				Default: PD1
PD1	115	VO	5VT	Alternate: EXMC_D3
151	110	,,	371	Remap: CAN0_TX, OSCOUT
				Default: PD2
PD2	116	VO	5VT	Alternate: TIMER2_ETI, UART4_RX
	<u> </u>			Default: PD3
PD3	117	VO	5VT	Alternate: EXMC_CLK
. 50	'''			Remap: USART1_CTS
	1			Default: PD4
PD4	118	VO	5VT	Alternate: EXMC_NOE
				Remap: USART1_RTS
				Default: PD5
PD5	119	VO	5VT	Alternate: EXMC_NWE
		1	<u> </u>	2/



Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				Remap: USART1_TX
V _{SS_10}	120	Р		Default: V _{SS_10}
V _{DD_10}	121	Р		Default: V _{DD_10}
PD6	122	VO	5VT	Default: PD6 Alternate: EXMC_NWAIT Remap: USART1_RX
PD7	123	VO	5VT	Default: PD7 Alternate: EXMC_NE0, EXMC_NCE1 Remap: USART1_CK
PG9	124	VO	5VT	Default: PG9 Alternate: EXMC_NE1, EXMC_NCE2
PG10	125	VO	5VT	Default: PG10 Alternate: EXMC_NCE3_0, EXMC_NE2
PG11	126	VO	5VT	Default: PG11 Alternate: EXMC_NCE3_1
PG12	127	VO	5VT	Default: PG12 Alternate: EXMC_NE3
PG13	128	VO	5VT	Default: PG13 Alternate: EXMC_A24
PG14	129	VO	5VT	Default: PG14 Alternate: EXMC_A25
V _{SS_11}	130	Р		Default: V _{SS_11}
$V_{DD_{-11}}$	131	Р		Default: V _{DD_11}
PG15	132	VO	5VT	Default: PG15
PB3	133	VO	5VT	Default: JTDO Alternate:SPI2_SCK, I2S2_CK Remap: PB3, TRACESWO, TIMER1_CH1, SPI0_SCK
PB4	134	VO	5VT	Default: NJTRST Alternate: SPI2_MISO Remap: TIMER2_CH0, PB4, SPI0_MISO
PB5	135	VO		Default: PB5 Alternate: I2C0_SMBA, SPI2_MOSI, I2S2_SD, ENET_MII_PPS_OUT, ENET_RMII_PPS_OUT Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX
PB6	136	VO	5VT	Default: PB6 Alternate: I2C0_SCL, TIMER3_CH0 Remap: USART0_TX, CAN1_TX, SPI0_IO2
PB7	137	VO	5VT	Default: PB7 Alternate: I2C0_SDA , TIMER3_CH1, EXMC_NA DV Remap: USART0_RX, SPI0_IO3
BOOT0	138	I		Default: BOOT0





Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				Default: PB8
PB8	139	VO	5VT	Alternate: TIMER3_CH2, TIMER9_CH0 ⁽³⁾ ,
1 50	100	,,	3 7 1	ENET_MII_TXD3
				Remap: I2C0_SCL, CAN0_RX
				Default: PB9
PB9	140	VO	5VT	Alternate: TIMER3_CH3, TIMER10_CH0 ⁽³⁾
				Remap: I2C0_SDA, CAN0_TX
PE0	141	VO	5VT	Default: PE0
PEU	141	10	571	Alternate: TIMER3_ETI, EXMC_NBL0
DE4	4.40		5\ /T	Default: PE1
PE1	142	VO	5VT	Alternate: EXMC_NBL1
V _{SS_3}	143	Р		Default: V _{SS_3}
V _{DD_3}	144	Р		Default: V _{DD_3}

Notes:

(1) Type: I = input, O = output, P = power.

(2)I/O Level: 5VT = 5 V tolerant.

(3) Functions are available in GD32F307ZG devices.



2.6.2. GD32F307Vx LQFP100 pin definitions

Table 2-4. GD32F307Vx LQFP100 pin definitions

			p c	
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
PE2	1	VO	5VT	Default: PE2 Alternate: TRACECK, EXMC_A23
PE3	2	VO	5VT	Default: PE3 Alternate: TRACED0, EXMC_A19
PE4	3	VO	5VT	Default: PE4 Alternate:TRACED1, EXMC_A20
PE5	4	<i>V</i> O	5VT	Default: PE5 Alternate:TRACED2, EXMC_A21 Remap: TIMER8_CH0 ⁽³⁾
PE6	5	VO	5VT	Default: PE6 Alternate:TRACED3, EXMC_A22 Remap: TIMER8_CH1 ⁽³⁾
V_{BAT}	6	Р		Default: V _{BAT}
PC13- TAMPER- RTC	7	VO		Default: PC13 Alternate: TAMPER-RTC
PC14- OSC32IN	8	VO		Default: PC14 Alternate: OSC32IN
PC15- OSC32OUT	9	VO		Default: PC15 Alternate: OSC32OUT
V _{SS_5}	10	Р		Default: V _{SS_5}
V_{DD_5}	11	Р		Default: V _{DD_5}
OSCIN	12	I		Default: OSCIN Remap: PD0
OSCOUT	13	0		Default: OSCOUT Remap: PD1
NRST	14	VO		Default: NRST
PC0	15	VO		Default: PC0 Alternate: ADC01_IN10
PC1	16	VO		Default: PC1 Alternate: ADC01_IN11, ENET_MDC
PC2	17	VO		Default: PC2 Alternate: ADC01_IN12, ENET_MII_TXD2
PC3	18	VO		Default: PC3 Alternate: ADC01_IN13, ENET_MII_TX_CLK
V _{SSA}	19	Р		Default: V _{SSA}
V _{REF} -	20	Р		Default: V _{REF} -
V _{REF+}	21	Р		Default: V _{REF+}



				ODOZI OOT XX Dalastice
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
V_{DDA}	22	Р		Default: V _{DDA}
· BBA				Default: PA0
PA0-WKUP	23	VO		Alternate: WKUP, USART1_CTS, ADC01_IN0, TIMER1_CH0, TIMER1_ETI, TIMER4_CH0, TIMER7_ETI ⁽⁴⁾ , ENET_MII_CRS
PA1	24	VO		Default: PA1 Alternate: USART1_RTS, ADC01_IN1, TIMER1_CH1, TIMER4_CH1, ENET_MII_RX_CLK, ENET_RMII_REF_CLK
PA2	25	VO		Default: PA2 Alternate: USART1_TX, ADC01_IN2, TIMER1_CH2, TIMER4_CH2, TIMER8_CH0 ⁽³⁾ , ENET_MDIO,SPI0_IO2
PA3	26	VO		Default: PA3 Alternate: USART1_RX, ADC01_IN3, TIMER1_CH3, TIMER4_CH3, TIMER8_CH1 ⁽³⁾ , ENET_MII_COL, SPI0_IO3
V _{SS_4}	27	Р		Default: V _{SS_4}
V _{DD_4}	28	Р		Default: V _{DD_4}
PA4	29	VO		Default: PA4 Alternate: SPI0_NSS, USART1_CK, ADC01_IN4, DAC_OUT0 Remap:SPI2_NSS, I2S2_WS
PA5	30	VO		Default: PA5 Alternate: SPI0_SCK, ADC01_IN5, DAC_OUT1
PA6	31	VO		Default: PA6 Alternate: SPI0_MISO, ADC01_IN6, TIMER2_CH0, TIMER7_BRKIN ⁽⁴⁾ , TIMER12_CH0 ⁽³⁾ Remap: TIMER0_BRKIN
PA7	32	VO		Default: PA7 Alternate: SPI0_MOSI, ADC01_IN7, TIMER2_CH1, TIMER7_CH0_ON ⁽⁴⁾ , TIMER13_CH0 ⁽³⁾ , ENET_MII_RX_DV, ENET_RMII_CRS_DV Remap: TIMER0_CH0_ON
PC4	33	VO		Default: PC4 Alternate: ADC01_IN14, ENET_MII_RXD0, ENET_RMII_RXD0
PC5	34	VO		Default: PC5 Alternate: ADC01_IN15, ENET_MII_RXD1, ENET_RMII_RXD1
PB0	35	VO		Default: PB0 Alternate: ADC01_IN8, TIMER2_CH2, TIMER7_CH1_ON ⁽⁴⁾ , ENET_MII_RXD2



				ODOZI 307 XX Dalastice
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				Remap: TIMER0_CH1_ON
				Default: PB1
PB1	36	VO		Alternate: ADC01_IN9, TIMER2_CH3, TIMER7_CH2_ON ⁽⁴⁾ , ENET_MII_RXD3 Remap: TIMER0_CH2_ON
PB2	37	VO	5VT	Default: PB2, BOOT1
PE7	38	VO	5VT	Default: PE7 Alternate: EXMC_D4 Remap: TIMER0_ETI
PE8	39	VO	5VT	Default: PE8 Alternate: EXMC_D5 Remap: TIMER0_CH0_ON
PE9	40	VO	5VT	Default: PE9 Alternate: EXMC_D6 Remap: TIMER0_CH0
PE10	41	VO	5VT	Default: PE10 Alternate: EXMC_D7 Remap: TIMER0_CH1_ON
PE11	42	VO	5VT	Default: PE11 Alternate: EXMC_D8 Remap: TIMER0_CH1
PE12	43	VO	5VT	Default: PE12 Alternate: EXMC_D9 Remap: TIMER0_CH2_ON
PE13	44	VO	5VT	Default: PE13 Alternate: EXMC_D10 Remap: TIMER0_CH2
PE14	45	VO	5VT	Default: PE14 Alternate: EXMC_D11 Remap: TIMER0_CH3
PE15	46	VO	5VT	Default: PE15 Alternate: EXMC_D12 Remap: TIMER0_BRKIN
PB10	47	VO	5VT	Default: PB10 Alternate: I2C1_SCL, USART2_TX, ENET_MII_RX_ER Remap: TIMER1_CH2
PB11	48	VO	5VT	Default: PB11 Alternate: I2C1_SDA, USART2_RX, ENET_MII_TX_EN, ENET_RMII_TX_EN Remap: TIMER1_CH3
V _{SS_1}	49	Р		Default: V _{SS_1}
V _{DD_1}	50	Р		Default: V _{DD_1}



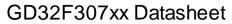
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
PB12	51	VO	5VT	Default: PB12 Alternate: SP1_NSS, I2C1_SMBA, USART2_CK, TIMER0_BRKIN, I2S1_WS, CAN1_RX, ENET_MII_TXD0, ENET_RMII_TXD0
PB13	52	VO	5VT	Default: PB13 Alternate: SP11_SCK, USART2_CTS, TIMER0_CH0_ON, I2S1_CK, CAN1_TX, ENET_MII_TXD1, ENET_RMII_TXD1
PB14	53	VO	5VT	Default: PB14 Alternate: SP1_MISO, USART2_RTS, TIMER0_CH1_ON, TIMER11_CH0 ⁽³⁾
PB15	54	VO	5VT	Default: PB15 Alternate: SP1_MOSI, TIMER0_CH2_ON, I2S1_SD, TIMER11_CH1 ⁽³⁾
PD8	55	VO	5VT	Default: PD8 Alternate: EXMC_D13 Remap: USART2_TX, ENET_MII_RX_DV, ENET_RMII_CRS_DV
PD9	56	VO	5VT	Default: PD9 Alternate: EXMC_D14 Remap: USART2_RX, ENET_MII_RXD0, ENET_RMII_RXD0
PD10	57	VO	5VT	Default: PD10 Alternate: EXMC_D15 Remap: USART2_CK, ENET_MII_RXD1, ENET_RMII_RXD1
PD11	58	VO	5VT	Default: PD11 Alternate: EXMC_A16 Remap: USART2_CTS, ENET_MII_RXD2
PD12	59	VO	5VT	Default: PD12 Alternate: EXMC_A17 Remap: TIMER3_CH0, USART2_RTS, ENET_MII_RXD3
PD13	60	VO	5VT	Default: PD13 Alternate: EXMC_A18 Remap: TIMER3_CH1
PD14	61	VO	5VT	Default: PD14 Alternate: EXMC_D0 Remap: TIMER3_CH2
PD15	62	VO	5VT	Default: PD15 Alternate: EXMC_D1 Remap: TIMER3_CH3, CTC_SYNC
PC6	63	VO	5VT	Default: PC6



				GD321 307 XX DataStilee
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				Alternate: I2S1_MCK, TIMER7_CH0 ⁽⁴⁾
				Remap: TIMER2_CH0
				Default: PC7
PC7	64	VO	5VT	Alternate: I2S2_MCK, TIMER7_CH1(4)
				Remap: TIMER2_CH1
		VO	5VT	Default: PC8
PC8	65			Alternate: TIMER7_CH2 ⁽⁴⁾
				Remap: TIMER2_CH2
				Default: PC9
PC9	66	VO	5VT	Alternate: TIMER7_CH3 ⁽⁴⁾
				Remap: TIMER2_CH3
			5VT	Default: PA8
PA8	67	VO		Alternate: USARTO_CK, TIMERO_CH0, CK_OUT0,
				USBFS_SOF, CTC_SYNC
				Default: PA9
PA9	68	VO	5VT	Alternate: USART0_TX, TIMER0_CH1,
				USBFS_VBUS
PA10	69	VO	5VT	Default: PA10
			3.1	Alternate: USART0_RX, TIMER0_CH2, USBFS_ID
		VO	5VT	Default: PA11
PA11	70			Alternate: USARTO_CTS, CANO_RX, USBFS_DM,
				TIMERO_CH3
D. 40		VO	5VT	Default: PA12
PA12	71			Alternate: USARTO_RTS, USBFS_DP, CANO_TX,
				TIMERO_ETI
PA13	72	VO	5VT	Default: JTMS, SWDIO Remap: PA13
NC	73			renap. FA13
	74	- Р	-	Default. V
V _{SS_2}		-		Default: V _{SS_2}
V_{DD_2}	75	Р		Default: V _{DD_2}
PA14	76	VO	5VT	Default: JTCK, SWCLK
		 		Remap: PA14
				Default: JTDI
PA15	77	VO	5VT	Alternate: SPI2_NSS, I2S2_WS
				Remap: TIMER1_CH0, TIMER1_ETI, PA15, SPI0_NSS
			5VT	Default: PC10
PC10	78	VO		Alternate: UART3_TX
	70	,,		Remap: USART2_TX, SPI2_SCK, I2S2_CK
	 			Default: PC11
PC11	79	VO	5VT	Alternate: UART3_RX
. 3	'			Remap: USART2_RX, SPI2_MISO
PC12	80	VO	5VT	Default: PC12
			<u> </u>	,



					ODOZI OOT XX Datastice
Pi	in Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
					Alternate: UART4_TX
					Remap: USART2_CK, SPI2_MOSI, I2S2_SD
	PD0	81	VO	5VT	Default: PD0 Alternate: EXMC_D2 Remap: CAN0_RX, OSCIN
	PD1	82	VO	5VT	Default: PD1 Alternate: EXMC_D3 Remap: CAN0_TX, OSCOUT
	PD2	83	VO	5VT	Default: PD2 Alternate: TIMER2_ETI, UART4_RX
	PD3	84	VO	5VT	Default: PD3 Alternate: EXMC_CLK Remap: USART1_CTS
	PD4	85	VO	5VT	Default: PD4 Alternate: EXMC_NOE Remap: USART1_RTS
	PD5	86	VO	5VT	Default: PD5 Alternate: EXMC_NWE Remap: USART1_TX
	PD6	87	VO	5VT	Default: PD6 Alternate: EXMC_NWAIT Remap: USART1_RX
	PD7	88	VO	5VT	Default: PD7 Alternate: EXMC_NE0, EXMC_NCE1 Remap: USART1_CK
	PB3	89	VO	5VT	Default: JTDO Alternate:SPI2_SCK, I2S2_CK Remap: PB3, TRACESWO, TIMER1_CH1, SPI0_SCK
	PB4	90	VO	5VT	Default: NJTRST Alternate: SPI2_MISO Remap: TIMER2_CH0, PB4, SPI0_MISO
	PB5	91	VO		Default: PB5 Alternate: I2C0_SMBA, SPI2_MOSI, I2S2_SD, ENET_MII_PPS_OUT, ENET_RMII_PPS_OUT Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX
	PB6	92	VO	5VT	Default: PB6 Alternate: I2C0_SCL, TIMER3_CH0 Remap: USART0_TX, CAN1_TX, SPI0_IO2
	PB7	93	VO	5VT	Default: PB7 Alternate: I2C0_SDA , TIMER3_CH1, EXMC_NA DV Remap: USART0_RX, SPI0_IO3
	BOOT0	94	I		Default: BOOT0





Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
PB8	95	VO	5VT	Default: PB8 Alternate: TIMER3_CH2, TIMER9_CH0 ⁽³⁾ , ENET_MII_TXD3 Remap: I2C0_SCL, CAN0_RX
PB9	96	VO	5VT	Default: PB9 Alternate: TIMER3_CH3, TIMER10_CH0 ⁽³⁾ Remap: I2C0_SDA, CAN0_TX
PE0	97	VO	5VT	Default: PE0 Alternate: TIMER3_ETI, EXMC_NBL0
PE1	98	VO	5VT	Default: PE1 Alternate: EXMC_NBL1
V _{SS_3}	99	Р		Default: V _{SS_3}
V _{DD_3}	100	Р		Default: V _{DD_3}

Notes:

(1) Type: I = input, O = output, P = power.

(2)I/O Level: 5VT = 5 V tolerant.

(3) Functions are available in GD32F307VG devices.

(4) Functions are available in GD32F307VE/G devices.



2.6.3. GD32F307Rx LQFP64 pin definitions

Table 2-5. GD32F307Rx LQFP64 pin definitions

Table 2-3.	0001.00	7110(= 4)		
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
V _{BAT}	1	Р		Default: V _{BAT}
PC13- TAMPER- RTC	2	VO		Default: PC13 Alternate: TAMPER-RTC
PC14- OSC32IN	3	VO		Default: PC14 Alternate: OSC32IN
PC15- OSC32OUT	4	VO		Default: PC15 Alternate: OSC32OUT
OSCIN	5	Ι		Default: OSCIN Remap: PD0 ⁽⁵⁾
OSCOUT	6	0		Default: OSCOUT Remap: PD1 ⁽⁵⁾
NRST	7	VO		Default: NRST
PC0	8	VO		Default: PC0 Alternate: ADC01_IN10
PC1	9	VO		Default: PC1 Alternate: ADC01_IN11, ENET_MDC
PC2	10	VO		Default: PC2 Alternate: ADC01_IN12, ENET_MII_TXD2
PC3	11	VO		Default: PC3 Alternate: ADC01_IN13, ENET_MII_TX_CLK
V_{SSA}	12	Р		Default: V _{SSA}
V_{DDA}	13	Р		Default: V _{DDA}
PA0-WKUP	14	VO		Default: PA0 Alternate: WKUP, USART1_CTS, ADC01_IN0, TIMER1_CH0, TIMER1_ETI, TIMER4_CH0, TIMER7_ETI ⁽⁴⁾ , ENET_MII_CRS
PA1	15	VO		Default: PA1 Alternate: USART1_RTS, ADC01_IN1, TIMER1_CH1, TIMER4_CH1, ENET_MII_RX_CLK, ENET_RMII_REF_CLK
PA2	16	VO		Default: PA2 Alternate: USART1_TX, ADC01_IN2, TIMER1_CH2, TIMER4_CH2, TIMER8_CH0 ⁽³⁾ , ENET_MDIO,SPI0_IO2
PA3	17	VO		Default: PA3 Alternate: USART1_RX, ADC01_IN3, TIMER1_CH3, TIMER4_CH3, TIMER8_CH1 ⁽³⁾ , ENET_MII_COL,



_					ODOZI OOTAX Datasrice
	Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
ľ					SPI0_IO3
f	V _{SS_4}	18	Р		Default: Vss 4
r	V _{DD_4}	19	P		Default: V _{DD} ₄
	PA4	20	VO		Default: PA4 Alternate: SPI0_NSS, USART1_CK, ADC01_IN4, DAC_OUT0 Remap:SPI2_NSS, I2S2_WS
	PA5	21	VO		Default: PA5 Alternate: SPI0_SCK, ADC01_IN5, DAC_OUT1
	PA6	22	VO		Default: PA6 Alternate: SPI0_MISO, ADC01_IN6, TIMER2_CH0, TIMER7_BRKIN ⁽⁴⁾ , TIMER12_CH0 ⁽³⁾ Remap: TIMER0_BRKIN
	PA7	23	VO		Default: PA7 Alternate: SPI0_MOSI, ADC01_IN7, TIMER2_CH1, TIMER7_CH0_ON ⁽⁴⁾ , TIMER13_CH0 ⁽³⁾ , ENET_MII_RX_DV, ENET_RMII_CRS_DV Remap: TIMER0_CH0_ON
	PC4	24	VO		Default: PC4 Alternate: ADC01_IN14, ENET_MII_RXD0, ENET_RMII_RXD0
	PC5	25	VO		Default: PC5 Alternate: ADC01_IN15, ENET_MII_RXD1, ENET_RMII_RXD1
	PB0	26	VO		Default: PB0 Alternate: ADC01_IN8, TIMER2_CH2, TIMER7_CH1_ON ⁽⁴⁾ , ENET_MII_RXD2 Remap: TIMER0_CH1_ON
	PB1	27	VO		Default: PB1 Alternate: ADC01_IN9, TIMER2_CH3, TIMER7_CH2_ON ⁽⁴⁾ , ENET_MII_RXD3 Remap: TIMER0_CH2_ON
Ĺ	PB2	28	VO	5VT	Default: PB2, BOOT1
	PB10	29	VO	5VT	Default: PB10 Alternate: I2C1_SCL, USART2_TX, ENET_MII_RX_ER Remap: TIMER1_CH2
	PB11	30	VO	5VT	Default: PB11 Alternate: I2C1_SDA, USART2_RX, ENET_MII_TX_EN, ENET_RMII_TX_EN Remap: TIMER1_CH3
ſ	V _{SS_1}	31	Р		Default: V _{SS_1}
ſ	V_{DD_1}	32	Р		Default: V _{DD_1}



_				ODSZI SOTAX Datastice
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
PB12	33	VO	5VT	Default: PB12 Alternate: SP1_NSS, I2C1_SMBA, USART2_CK, TIMER0_BRKIN, I2S1_WS, CAN1_RX, ENET_MII_TXD0, ENET_RMII_TXD0
PB13	34	VO	5VT	Default: PB13 Alternate: SP1_SCK, USART2_CTS, TIMER0_CH0_ON, I2S1_CK, CAN1_TX, ENET_MII_TXD1, ENET_RMII_TXD1
PB14	35	VO	5VT	Default: PB14 Alternate: SP1_MISO, USART2_RTS, TIMER0_CH1_ON, TIMER11_CH0 ⁽³⁾
PB15	36	VO	5VT	Default: PB15 Alternate: SP1_MOSI, TIMER0_CH2_ON, I2S1_SD, TIMER1_1_CH1 ⁽³⁾
PC6	37	VO	5VT	Default: PC6 Alternate: I2S1_MCK, TIMER7_CH0 ⁽⁴⁾ Remap: TIMER2_CH0
PC7	38	VO	5VT	Default: PC7 Alternate: I2S2_MCK, TIMER7_CH1 ⁽⁴⁾ Remap: TIMER2_CH1
PC8	39	VO	5VT	Default: PC8 Alternate: TIMER7_CH2 ⁽⁴⁾ Remap: TIMER2_CH2
PC9	40	VO	5VT	Default: PC9 Alternate: TIMER7_CH3 ⁽⁴⁾ Remap: TIMER2_CH3
PA8	41	VO	5VT	Default: PA8 Alternate: USART0_CK, TIMER0_CH0, CK_OUT0, USBFS_SOF, CTC_SYNC
PA9	42	VO	5VT	Default: PA9 Alternate: USART0_TX, TIMER0_CH1, USBFS_VBUS
PA10	43	VO	5VT	Default: PA10 Alternate: USART0_RX, TIMER0_CH2, USBFS_ID
PA11	44	VO	5VT	Default: PA11 Alternate: USART0_CTS, CAN0_RX, USBFS_DM, TIMER0_CH3
PA12	45	VO	5VT	Default: PA12 Alternate: USART0_RTS, USBFS_DP, CAN0_TX, TIMER0_ETI
PA13	46	VO	5VT	Default: JTMS, SWDIO Remap: PA13
V _{SS_2}	47	Р		Default: V _{SS_2}



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Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
V_{DD_2}	48	Р		Default: V _{DD 2}
				Default: JTCK, SWCLK
PA14	49	VO	5VT	Remap: PA14
PA15	50	VO	5VT	Default: JTDI Alternate: SPI2_NSS, I2S2_WS Remap: TIMER1_CH0, TIMER1_ETI, PA15, SPI0_NSS
PC10	51	VO	5VT	Default: PC10 Alternate: UART3_TX Remap: USART2_TX, SPI2_SCK, I2S2_CK
PC11	52	VO	5VT	Default: PC11 Alternate: UART3_RX Remap: USART2_RX, SPI2_MISO
PC12	53	VO	5VT	Default: PC12 Alternate: UART4_TX Remap: USART2_CK, SPI2_MOSI, I2S2_SD
PD2	54	VO	5VT	Default: PD2 Alternate: TIMER2_ETI, UART4_RX
PB3	55	VO	5VT	Default: JTDO Alternate:SPI2_SCK, I2S2_CK Remap: PB3, TRACESWO, TIMER1_CH1, SPI0_SCK
PB4	56	VO	5VT	Default: NJTRST Alternate: SPI2_MISO Remap: TIMER2_CH0, PB4, SPI0_MISO
PB5	57	VO		Default: PB5 Alternate: I2C0_SMBA, SPI2_MOSI, I2S2_SD, ENET_MII_PPS_OUT, ENET_RMII_PPS_OUT Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX
PB6	58	VO	5VT	Default: PB6 Alternate: I2C0_SCL, TIMER3_CH0 Remap: USART0_TX, CAN1_TX, SPI0_IO2
PB7	59	VO	5VT	Default: PB7 Alternate: I2C0_SDA , TIMER3_CH1 Remap: USART0_RX, SPI0_IO3
воото	60	I		Default: BOOT0
PB8	61	VO	5VT	Default: PB8 Alternate: TIMER3_CH2, TIMER9_CH0 ⁽³⁾ , ENET_MII_TXD3 Remap: I2C0_SCL, CAN0_RX
PB9	62	VO	5VT	Default: PB9 Alternate: TIMER3_CH3, TIMER10_CH0 ⁽³⁾ Remap: I2C0_SDA, CAN0_TX





Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
V _{SS_3}	63	Р		Default: V _{SS_3}
V _{DD_3}	64	Р		Default: V _{DD_3}

Notes:

(1) Type: I = input, O = output, P = power.

(2)I/O Level: 5VT = 5 V tolerant.

(3) Functions are available in GD32F307RG devices.

(4)Functions are available in GD32F307RE/G devices.

(5)PD0/PD1 cannot be used for EXTI in this package.



3. Functional description

3.1. Arm[®] Cortex[®]-M4 core

The Arm® Cortex®-M4 processor is a high performance embedded processor with DSP instructions which allow efficient signal processing and complex algorithm execution. It brings an efficient, easy-to-use blend of control and signal processing capabilities to meet the digital signal control markets demand. The processor is highly configurable enabling a wide range of implementations from those requiring floating point operations, memory protection and powerful trace technology to cost sensitive devices requiring minimal area, while delivering outstanding computational performance and an advanced system response to interrupts.

32-bit Arm® Cortex®-M4 processor core

- Up to 120 MHz operation frequency
- Single-cycle multiplication and hardware divider
- Integrated DSP instructions
- Integrated Nested Vectored Interrupt Controller (NVIC)
- 24-bit SysTick timer

The Cortex®-M4 processor is based on the Armv7-M architecture and supports both Thumb and Thumb-2 instruction sets. Some system peripherals listed below are also provided by Cortex®-M4:

- Internal Bus Matrix connected with ICode bus, DCode bus, System bus, Private Peripheral Bus (PPB) and debug accesses (AHB-AP)
- Nested Vectored Interrupt Controller (NVIC)
- Flash Patch and Breakpoint (FPB)
- Data Watchpoint and Trace (DWT)
- Instrument Trace Macrocell (ITM)
- Memory Protection Unit (MPU)
- Serial Wire JTAG Debug Port (SWJ-DP)
- Trace Port Interface Unit (TPIU)
- Floating Point Unit (FPU)

3.2. On-chip memory

- Up to 1024 Kbytes of Flash memory, including code Flash and data Flash
- 96 KB of SRAM

The Arm® Cortex®-M4 processor is structured in Harvard architecture which can use separate buses to fetch instructions and load/store data. 1024 Kbytes of inner flash at most, which includes code Flash that available for storing programs and data, and accessed (R/W) at CPU clock speed with zero wait states. An extra data Flash is also included for storing data mainly. *Table 2-2. GD32F307xx memory map* shows the memory of the GD32F307xx series of



devices, including Flash, SRAM, peripheral, and other pre-defined regions.

3.3. Clock, reset and supply management

- Internal 8 MHz factory-trimmed RC and external 4 to 32 MHz crystal oscillator
- Internal 48 MHz RC oscillator
- Internal 40 KHz RC calibrated oscillator and external 32.768 KHz crystal oscillator
- 2.6 to 3.6 V application supply and I/Os
- Supply Supervisor: POR (Power On Reset), PDR (Power Down Reset), and low voltage detector (LVD)

The Clock Control Unit (CCU) provides a range of oscillator and clock functions. These include internal RC oscillator and external crystal oscillator, high speed and low speed two types. Several prescalers allow the frequency configuration of the AHB and two APB domains. The maximum frequency of the two AHB domains are 120 MHz The maximum frequency of the two APB domains including APB1 is 60 MHz and APB2 is 120 MHz See <u>Figure 2-5</u> <u>GD32F307xx clock tree</u> for details on the clock tree.

The Reset Control Unit (RCU) controls three kinds of reset: system reset resets the processor core and peripheral IP components. Power-on reset (POR) and power-down reset (PDR) are always active, and ensures proper operation starting from/down to 2.6 V. The device remains in reset mode when V_{DD} is below a specified threshold. The embedded low voltage detector (LVD) monitors the power supply, compares it to the voltage threshold and generates an interrupt as a warning message for leading the MCU into security.

Power supply schemes:

- V_{DD} range: 2.6 to 3.6 V, external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} range: 2.6 to 3.6 V, external analog power supplies for ADC, reset blocks, RCs and PLL. V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS}, respectively.
- V_{BAT} range: 1.8 to 3.6 V, power supply for RTC, external clock 32 KHz oscillator and backup registers (through power switch) when V_{DD} is not present.

3.4. Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from main flash memory (default)
- Boot from system memory
- Boot from on-chip SRAM

The boot loader is located in the internal boot ROM memory (system memory). It is used to reprogram the Flash memory by using USART0 (PA9 and PA10), USART1 (PD5 and PD6) and USBFS (PA9, PA11 and PA12) is also available for boot functions. It also can be used to transfer and update the Flash memory code, the data and the vector table sections. In default



condition, boot from bank0 of Flash memory is selected. It also supports to boot from bank1 of Flash memory by setting a bit in option bytes.

3.5. Power saving modes

The MCU supports three kinds of power saving modes to achieve even lower power consumption. They are sleep mode, deep-sleep mode and standby mode. These operating modes reduce the power consumption and allow the application to achieve the best balance between the CPU operating time, speed and power consumption.

■ Sleep mode

In sleep mode, only the clock of CPU core is off. All peripherals continue to operate and any interrupt/event can wake up the system.

■ **Deep-sleep** mode

In deep-sleep mode, all clocks in the 1.2V domain are off, and all of the high speed crystal oscillator (IRC8M, HXTAL) and PLL are disabled. Only the contents of SRAM and registers are retained. Any interrupt or wakeup event from EXTI lines can wake up the system from the deep-sleep mode including the 16 external lines, the RTC alarm, the LVD output, the USB wakeup and ENET wakeup. When exiting the deep-sleep mode, the IRC8M is selected as the system clock.

Standby mode

In standby mode, the whole 1.2V domain is power off, the LDO is shut down, and all of IRC8M, HXTAL and PLL are disabled. The contents of SRAM and registers (except backup registers) are lost. There are four wakeup sources for the standby mode, including the external reset from NRST pin, the RTC, the FWDG reset, and the rising edge on WKUP pin.

3.6. Analog to digital converter (ADC)

- 12-bit SAR ADC's conversion rate is up to 2.6 MSPS
- 12-bit, 10-bit, 8-bit or 6-bit configurable resolution
- Hardware oversampling ratio adjustable from 2 to 256x improves resolution to 16-bit
- Input voltage range: V_{SSA} to V_{DDA} (2.6 to 3.6 V)
- Temperature sensor

Up to two 12-bit 2.6 MSPS multi-channel ADCs are integrated in the device. It has a total of 18 multiplexed channels: 16 external channels, 1 channel for internal temperature sensor (V_{SENSE}), and 1 channel for internal reference voltage (V_{REFINT}). The input voltage range is between 2.6 V and 3.6 V. An on-chip hardware oversampling scheme improves performance while off-loading the related computational burden from the CPU. An analog watchdog block can be used to detect the channels, which are required to remain within a specific threshold window. A configurable channel management block can be used to perform conversions in single, continuous, scan or discontinuous mode to support more advanced use.



The ADC can be triggered from the events generated by the general level 0 timers (TIMERx) and the advanced timers (TIMER0 and TIMER7) with internal connection. The temperature sensor can be used to generate a voltage that varies linearly with temperature. It is internally connected to the ADC_IN16 input channel which is used to convert the sensor output voltage in a digital value.

3.7. Digital to analog converter (DAC)

- Two 12-bit DACs with independent output channels
- 8-bit or 12-bit mode in conjunction with the DMA controller

The two 12-bit buffered DACs are used to generate variable analog outputs. The DAC channels can be triggered by the timer or EXTI with DMA support. In dual DAC channel operation, conversions could be done independently or simultaneously. The maximum output value of the DAC is $V_{\text{REF+}}$.

3.8. DMA

- 7 channel DMA0 controller and 5 channel DMA1 controller
- Peripherals supported: Timers, ADC, SPIs, I2Cs, USARTs, DAC, I2S

The flexible general-purpose DMA controllers provide a hardware method of transferring data between peripherals and/or memory without intervention from the CPU, thereby freeing up bandwidth for other system functions. Three types of access method are supported: peripheral to memory, memory to peripheral, memory to memory

Each channel is connected to fixed hardware DMA requests. The priorities of DMA channel requests are determined by software configuration and hardware channel number. Transfer size of source and destination are independent and configurable.

3.9. General-purpose inputs/outputs (GPIOs)

- Up to 112 fast GPIOs, all mappable on 16 external interrupt lines
- Analog input/output configurable
- Alternate function input/output configurable

There are up to 112 general purpose I/O pins (GPIO) in GD32F307xx, named PA0 ~ PA15 and PB0 ~ PB15, PC0 ~ PC15, PD0 ~ PD15, PE0 ~ PE15, PF0-PF15, PG0-PG15 to implement logic input/output functions. Each of the GPIO ports has related control and configuration registers to satisfy the requirements of specific applications. The external interrupts on the GPIO pins of the device have related control and configuration registers in the Interrupt/event controller (EXTI). The GPIO ports are pin-shared with other alternative functions (AFs) to obtain maximum flexibility on the package pins. Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-



up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high-current capable except for analog inputs.

3.10. Timers and PWM generation

- Two 16-bit advanced timer (TIMER0 & TIMER7), ten 16-bit general timers (TIMER1 ~ TIMER4, TIMER8 ~ TIMER13), and two 16-bit basic timer (TIMER5 & TIMER6)
- Up to 4 independent channels of PWM, output compare or input capture for each general timer and external trigger input
- 16-bit, motor control PWM advanced timer with programmable dead-time generation for output match
- Encoder interface controller with two inputs using quadrature decoder
- 24-bit SysTick timer down counter
- 2 watchdog timers (Free watchdog timer and window watchdog timer)

The advanced timer (TIMER0 & TIMER7) can be used as a three-phase PWM multiplexed on 6 channels. It has complementary PWM outputs with programmable dead-time generation. It can also be used as a complete general timer. The 4 independent channels can be used for input capture, output compare, PWM generation (edge-aligned or center-aligned counting modes) and single pulse mode output. If configured as a general 16-bit timer, it has the same functions as the TIMERx timer. It can be synchronized with external signals or to interconnect with other general timers together which have the same architecture and features.

The general timer, can be used for a variety of purposes including general time, input signal pulse width measurement or output waveform generation such as a single pulse generation or PWM output, up to 4 independent channels for input capture/output compare. TIMER1 ~ TIMER4 is based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. TIMER8 ~ TIMER13 is based on a 16-bit auto-reload upcounter and a 16-bit prescaler. The general timer also supports an encoder interface with two inputs using quadrature decoder.

The basic timer, known as TIMER5 & TIMER6, are mainly used for DAC trigger generation. They can also be used as a simple 16-bit time base.

The GD32F307xx have two watchdog peripherals, free watchdog timer and window watchdog timer. They offer a combination of high safety level, flexibility of use and timing accuracy.

The free watchdog timer includes a 12-bit down-counting counter and an 8-bit prescaler, It is clocked from an independent 40 KHz internal RC and as it operates independently of the main clock, it can operate in deep-sleep and standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management.

The window watchdog timer is based on a 7-bit down counter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early wakeup interrupt capability and the counter can be frozen in



debug mode.

The SysTick timer is dedicated for OS, but could also be used as a standard down counter.

The features are shown below:

- A 24-bit down counter
- Auto reload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source

3.11. Real time clock (RTC)

- 32-bit up-counter with a programmable 20-bit prescaler
- Alarm function
- Interrupt and wakeup event

The real time clock is an independent timer which provides a set of continuously running counters which can be used with suitable software to provide a clock calendar function, and provides an alarm interrupt and an expected interrupt. The RTC features a 32-bit programmable counter for long-term measurement using the compare register to generate an alarm. A 20-bit prescaler is used for the time base clock and is by default configured to generate a time base of 1 second from a clock at 32.768 KHz from external crystal oscillator.

3.12. Inter-integrated circuit (I2C)

- Up to two I2C bus interfaces can support both master and slave mode with a frequency up to 1 MHz (Fast mode plus)
- Provide arbitration function, optional PEC (packet error checking) generation and checking
- Supports 7-bit and 10-bit addressing mode and general call addressing mode

The I2C interface is an internal circuit allowing communication with an external I2C interface which is an industry standard two line serial interface used for connection to external hardware. These two serial lines are known as a serial data line (SDA) and a serial clockline (SCL). The I2C module provides several data transfer rates of up to 100 KHz in standard mode, up to 400 KHz in fast mode and up to 1 MHz in the fast mode plus. The I2C module also has an arbitration detect function to prevent the situation where more than one master attempts to transmit data to the I2C bus at the same time. A CRC-8 calculatoris also provided in I2C interface to perform packet error checking for I2C data.

3.13. Serial peripheral interface (SPI)

- Up to three SPI interfaces with a frequency of up to 30 MHz
- Support both master and slave mode



- Hardware CRC calculation and transmit automatic CRC error checking
- Quad-SPI configuration available in master mode (only in SPI0)

The SPI interface uses 4 pins, among which are the serial data input and output lines (MISO & MOSI), the clock line (SCK) and the slave select line (NSS). Both SPIs can be served by the DMA controller. The SPI interface may be used for a variety of purposes, including simplex synchronous transfers on two lines with a possible bidirectional data line or reliable communication using CRC checking. Quad-SPI master mode is also supported in SPI0.

3.14. Universal synchronous asynchronous receiver transmitter (USART)

- Up to three USARTs and two UARTs with operating frequency up to 7.5M Bits/s
- Supports both asynchronous and clocked synchronous serial communication modes
- IrDA SIR encoder and decoder support
- LIN break generation and detection
- USARTs support ISO 7816-3 compliant smart card interface

The USART (USART0, USART1 and USART2) and UART (UART3 & UART4) are used to translate data between parallel and serial interfaces, provides a flexible full duplex data exchange using synchronous or asynchronous transfer. It is also commonly usedforRS-232 standard communication. The USART/UART includes a programmable baud rate generator which is capable of dividing the system clock to produce a dedicated clock for the USART transmitter and receiver. The USART/UART also supports DMA function for high speed data communication except UART4.

3.15. Inter-IC sound (I2S)

- Two I2S bus Interfaces with sampling frequency from 8 KHz to 192 KHz
- Support either master or slave mode

The Inter-IC sound (I2S) bus provides a standard communication interface for digital audio applications by 3-wire serial lines. GD32F307xx contain two I2S-bus interfaces that can be operated with 16/32 bit resolution in master or slave mode, pin multiplexed with SPI1 and SPI2. The audio sampling frequency from 8 KHz to 192 KHz is supported.

3.16. Universal serial bus full-speed interface (USBFS)

- One USB device/host/full-speed Interface with frequency up to 12 Mbit/s
- Internal 48 MHz oscillator (IRC48M) support crystal-less operation
- Internal main PLL for USBCLK compliantly
- Internal USBFS PHY support



The Universal Serial Bus (USB) is a 4-wire bus with 4 bidirectional endpoints. The device controller enables 12 Mbit/s data exchange with integrated transceivers. Transaction formatting is performed by the hardware, including CRC generation and checking. It supports both host and device modes, as well as OTG mode with Host Negotiation Protocol (HNP) and Session Request Protocol (SRP). The controller contains a full-speed USB PHY internal. For full-speed or low-speed operation, no more external PHY chip is needed. It supports all the four types of transfer (control, bulk, Interrupt and isochronous) defined in USB 2.0 protocol. The required precise 48 MHz clock which can be generated from the internal main PLL (the clock source must use an HXTAL crystal oscillator) or by the internal 48 MHz oscillator (IRC48M) in automatic trimming mode that allows crystal-less operation.

3.17. Controller area network (CAN)

- Two CAN2.0B interface with communication frequency up to 1 Mbit/s
- Internal main PLL for CAN CLK compliantly

Controller area network (CAN) is a method for enabling serial communication in fieldbus. The CAN protocol has been used extensively in industrial automation and automotive applications. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Each CAN has three mailboxes for transmission and two FIFOs of three message deep for reception. It also provides 28 scalable/configurable identifier filter banks for selecting the incoming messages needed and discarding the others.

3.18. Ethernet (ENET)

- IEEE 802.3 compliant media access controller (MAC) for Ethernet LAN
- 10/100 Mbit/s rates with dedicated DMA controller and SRAM
- Support hardware precision time protocol (PTP) with conformity to IEEE 1588

The Ethernet media access controller (MAC) conforms to IEEE 802.3 specifications and fully supports IEEE 1588 standards. The embedded MAC provides the interface to the required external network physical interface (PHY) for LAN bus connection via an internal media independent interface (MII) or a reduced media independent interface (RMII). The number of MII signals provided up to 16 with 25 MHz output and RMII up to 7 with 50 MHz output. The function of 32-bit CRC checking is also available.

3.19. External memory controller (EXMC)

- Supported external memory: SRAM, PSRAM, ROM and NOR-Flash, NAND Flash and PC card
- Provide ECC calculating hardware module for NAND Flash memory block
- Up to 16-bit data bus
- Support to interface with Motorola 6800 and Intel 8080 type LCD directly



External memory controller (EXMC) is an abbreviation of external memory controller. It is divided in to several sub-banks for external device support, each sub-bank has its own chip selection signal but at one time, only one bank can be accessed. The EXMC support code execution from external memory except NAND Flash and PC card. The EXMC also can be configured to interface with the most common LCD module of Motorola 6800 and Intel 8080 series and reduce the system cost and complexity.

3.20. Debug mode

■ Serial wire JTAG debug port (SWJ-DP)

The Arm® SWJ-DP Interface is embedded and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

3.21. Package and operation temperature

- LQFP144 (GD32F307Zx), LQFP100 (GD32F307Vx) and LQFP64 (GD32F307Rx)
- Operation temperature range: -40°C to +85°C (industrial level)



4. Electrical characteristics

4.1. Absolute maximum ratings

The maximum ratings are the limits to which the device can be subjected without permanently damaging the device. Note that the device is not guaranteed to operate properly at the maximum ratings. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

Table 4-1. Absolute maximum ratings(1) (4)

Symbol	Parameter	Min	Max	Unit
V_{DD}	External voltage range ⁽²⁾	V _{SS} - 0.3	V _{SS} + 3.6	V
V_{DDA}	External analog supply voltage	V _{SSA} - 0.3	V _{SSA} + 3.6	V
V_{BAT}	External battery supply voltage	V _{SS} - 0.3	V _{SS} + 3.6	V
V	Input voltage on 5V tolerant pin ⁽³⁾	V _{SS} - 0.3	V _{DD} + 3.6	V
V _{IN}	Input voltage on other I/O	V _{SS} - 0.3	3.6	V
ΔV _{DDx}	Variations between different V _{DD} power pins		50	mV
V _{SSX} -V _{SS}	Variations between different ground pins		50	mV
lio	Maximum current for GPIO pins		±25	mA
T _A	Operating temperature range	-40	+85	°C
T _{STG}	Storage temperature range	-55	+150	°C
TJ	Maximum junction temperature		125	°C

 $[\]hbox{ (1). Guaranteed by design, not tested in production.} \\$

4.2. Operating conditions characteristics

Table 4-2. DC operating conditions

Symbol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
V_{DD}	Supply voltage		2.6	3.3	3.6	V
V_{DDA}	Analog supply voltage	Same as V _{DD}	2.6	3.3	3.6	V
V_{BAT}	Battery supply voltage		1.8		3.6	V

^{(1).} Based on characterization, not tested in production.

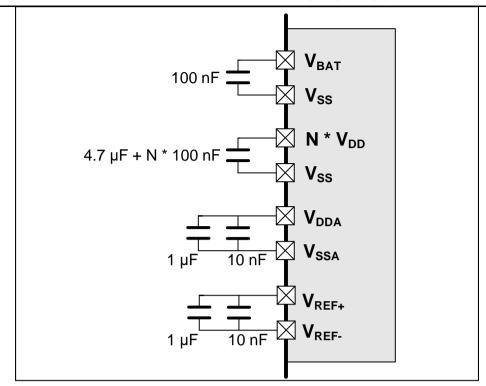
Figure 4-1. Recommended power supply decoupling capacitors⁽¹⁾⁽²⁾

^{(2).} All main power and ground pins should be connected to an external power source within the allowable range.

^{(3).} V_{IN} maximum value cannot exceed 6.5 V.

^{(4).} It is recommended that V_{DD} and V_{DDA} are powered by the same source. The maximum difference between V_{DD} and V_{DDA} does not exceed 300 mV during power-up and operation.





- (1). The V_{REF+} and V_{REF+} pins are only available on no less than 100-pin packages, or else the V_{REF+} and V_{REF+} pins are not available and internally connected to V_{DDA} and V_{SSA} pins.
- (2). All decoupling capacitors need to be as close as possible to the pins on the PCB board.

Table 4-3. Clock frequency(1)

Symbol	Parameter	Conditions	Min	Max	Unit
f _{HCLK}	AHB clock frequency			120	MHz
f _{APB1}	APB1 clock frequency			60	MHz
f _{APB2}	APB2 clock frequency		_	120	MHz

(1). Guaranteed by design, not tested in production.

Table 4-4. Operating conditions at Power up/ Power down(1)

Symbol	Parameter	Conditions	Min	Max	Unit
t _{VDD}	V _{DD} rise time rate		0	8	us/ V
	V _{DD} fall time rate	_	20	∞	µs/ V

(1). Guaranteed by design, not tested in production.

Table 4-5. Start-up timings of Operating conditions(1)(2)(3)

Symbol	Parameter	Conditions	Тур	Unit	
t _{start-up}	Start-up time	Clock source from HXTAL	154		
		Clock source from IRC8M	154	ms	

- (1). Based on characterization, not tested in production.
- (2). After power-up, the start-up time is the time between the rising edge of NRST high and the main function.
- (3). PLL isoff.



Table 4-6. Power saving mode wakeup timings characteristics(1) (2)

Symbol Parameter		Тур	Unit
t _{Sleep}	Wakeup from Sleep mode	3.4	
4	Wakeup from Deep-sleep mode (LDO On)	5.8	μs
tDeep-sleep	Wakeup from Deep-sleep mode (LDO in low power mode)	5.8	
t _{Standby}	Wakeup from Standby mode	154	ms

^{(1).} Based on characterization, not tested in production.

4.3. Power consumption

The power measurements specified in the tables represent that code with data executing from on-chip Flash with the following specifications.

Table 4-7. Power consumption characteristics (2)(3)(4)(5)

Symbol	Parameter	Conditions	Min	Typ ⁽¹⁾	Max	Unit
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$ System clock = 120 MHz, All peripherals enabled	_	45.1		mA
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$ System clock = 120 MHz, All peripherals disabled	_	25.5	_	mA
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$ System clock = 108 MHz, All peripherals enabled		40.7	_	mA
	Supply current (Run mode)	$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$ System clock = 108 MHz, All peripherals disabled	ı	23.2	_	mA
I _{DD} +I _{DDA}		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$ System clock = 96 MHz, All peripherals enabled	l	36.4		mA
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$ System clock = 96 MHz, All peripherals disabled	ı	20.8		mA
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$ System clock = 72 MHz, All peripherals enabled		27.9	_	mA
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$ System clock = 72 MHz, All peripherals disabled	_	16.1	_	mA
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$ System clock = 48 MHz, All peripherals enabled	_	19.3	_	mA

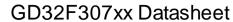
^{(2).} The wakeup time is measured from the wakeup event to the point at which the application code reads the first instruction under the below conditions: $V_{DD} = V_{DDA} = 3.3 \text{ V}$, IRC8M = System clock = 8 MHz.



Sym bol	Parameter	Conditions	Min	Typ ⁽¹⁾	Max	Unit
- Cylli DOI	T di dill'oto!			тур	Max	Onic
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$		11 /		mΛ
		System clock = 48 MHz, All peripherals		11.4	_	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$		45.0		
		System clock = 36 MHz, All peripherals	_	15.0	_	mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$				
		System clock = 36 MHz, All peripherals	_	9.1	_	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$				
		System clock = 24 MHz, All peripherals	_	10.6	_	mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$				
		System clock = 24 MHz, All peripherals	_	6.7	_	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$				
		System clock = 16 MHz, All peripherals	_	7.8	_	mΑ
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$				
		System clock = 16 MHz, All peripherals	_	5.2	_	mΑ
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$				
		System clock = 8 MHz, All peripherals	_	4.9	—	mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$				
		System clock = 8 MHz, All peripherals	_	3.6	_	mΑ
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 4 \text{ MHz},$				
		System clock = 4 MHz, All peripherals	_	1.4	_	mΑ
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 4 \text{ MHz},$				
		System clock = 4 MHz, All peripherals	_	0.9	_	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 2 \text{ MHz},$				
		System clock = 2 MHz, All peripherals	_	0.8	_	mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 2 \text{ MHz},$				
		System Clock = 2 MHz, All peripherals	_	0.6	_	mA
		disabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
	Supply current	System Clock = 120 MHz, CPU clock off,	_	31.4	_	mA
	(Sleep mode)	All peripherals enabled				
	1	1 1 22 2 22 2	I	<u> </u>		<u> </u>



Symbol	Parameter	Conditions	Min	Typ ⁽¹⁾	Max	Unit
•		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,		- 71		
		System Clock = 120 MHz, CPU clock off,	_	10.5	_	mA
		All peripherals disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{ HXTAL} = 25 \text{ MHz},$				
		System Clock = 108 MHz, CPU clock off,	_	28.4	_	mA
		All peripherals enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{ HXTAL} = 25 \text{ MHz},$				
		System Clock = 108 MHz, CPU clock off,	_	9.6	_	mA
		All peripherals disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$				
		System Clock = 96 MHz, CPU clock off, All	_	25.5	_	mA
		peripherals enabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 96 MHz, CPU clock off, All	_	8.8	_	mA
		peripherals disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System Clock = 72 MHz, CPU clock off, All	_	19.7	_	mA
		peripherals enabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 72 MHz, CPU clock off, All	_	7.1	_	mA
		peripherals disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System Clock = 48 MHz, CPU clock off, All	_	13.8	_	mΑ
		peripherals enabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 48 MHz, CPU clock off, All	_	5.4	_	mΑ
		peripherals disabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 36 MHz, CPU clock off, All	_	10.8	_	mΑ
		peripherals enabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 36 MHz, CPU clock off, All	_	4.5	_	mΑ
		peripherals disabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 24 MHz, CPU clock off, All	_	7.9	_	mA
		peripherals enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$				
		System Clock = 24 MHz, CPU clock off, All	_	3.7	_	mA
		peripherals disabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				_
		System Clock = 16 MHz, CPU clock off, All	_	5.9	_	mA
		peripherals enabled			_	





	Symbol	Parameter	Conditions	Min	Typ ⁽¹⁾	Max	Unit
ŀ			V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,		,		
			System Clock = 16 MHz, CPU clock off, All	_	3.2	_	mA
			peripherals disabled				
			V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
			System Clock = 8 MHz, CPU clock off, All	_	4.0		mA
			peripherals enabled				
			V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
			System Clock = 8 MHz, CPU clock off, All	_	2.6	_	mA
			peripherals disabled				
			$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 4 \text{ MHz,}$				
			System Clock = 4 MHz, CPU clock off, All	_	1.0	_	mΑ
			peripherals enabled				
			$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 4 \text{ MHz},$				
			System Clock = 4 MHz, CPU clock off, All	_	0.5	_	mΑ
			peripherals disabled				
			$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 2 \text{ MHz},$				
			System Clock = 2 MHz, CPU clock off, All	_	0.6	_	mA
			peripherals enabled				
			$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 2 \text{ MHz},$				
			System Clock = 2 MHz, CPU clock off, All	_	0.3	_	mΑ
			peripherals disabled				
			$V_{DD} = V_{DDA} = 3.3 \text{ V}$, LDO in run mode,				
			IRC40K off, RTC off, All GPIOs analog	_	137.8	1100	μΑ
			mode				
			$V_{DD} = V_{DDA} = 3.3 \text{ V}$, LDO in low power				
		Supply current	mode, IRC40K off, RTC off, All GPIOs	_	109.1	1100	μΑ
		(Deep-Sleep	analog mode				
		mode)	$V_{DD} = V_{DDA} = 3.3 \text{ V}$, Main LDO in under				
			drive mode, IRC40K off, RTC off, All		124.2	1100	μΑ
			GPIOs analog mode				
			$V_{DD} = V_{DDA} = 3.3 \text{ V}$, Low Power LDO in		04.5	4400	
			under drive mode, IRC40K off, RTC off, All	_	94.9	1100	μΑ
			GPIOs analog mode				
			$V_{DD} = V_{DDA} = 3.3 \text{ V, LXTAL off, IRC40K}$ on,	_	5.2	22	μΑ
			RTC on				
		Supply current	$V_{DD} = V_{DDA} = 3.3 \text{ V, LXTAL off, IRC40K on,}$				
		(Standby mode)	RTC off	_	4.9	22	μΑ
		,					
			$V_{DD} = V_{DDA} = 3.3 \text{ V, LXTAL off, IRC40K off,}$	_	4.3	22	μΑ
ļ			RTC off				
		Battery supply	V_{DD} off, V_{DDA} off, $V_{BAT} = 3.6 \text{ V}$, LXTAL on				
	I BAT	current (Backup	with external crystal, RTC on, LXTAL High	_	1.7	_	μΑ
		mode)	driving				

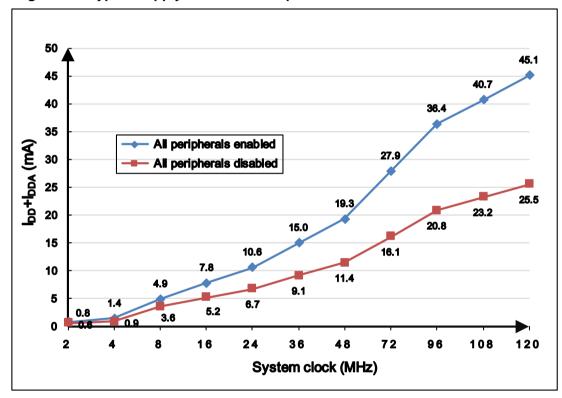


		OBOZI			alas	
Symbol	Param eter Param eter	Conditions	Min	Typ ⁽¹⁾	Max	Unit
		V_{DD} off, V_{DDA} off, V_{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL High driving	_	1.5		μΑ
		V _{DD} off, V _{DDA} off, V _{BAT} = 2.6 V, LXTAL on with external crystal, RTC on, LXTAL High driving	_	1.3	_	μΑ
		V _{DD} off, V _{DDA} off, V _{BAT} = 1.8 V, LXTAL on with external crystal, RTC on, LXTAL High driving	_	1.2	_	μΑ
		V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving	_	1.4	_	μΑ
		V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving	_	1.2	_	μΑ
		V _{DD} off, V _{DDA} off, V _{BAT} = 2.6 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving	_	1.1	_	μΑ
		V _{DD} off, V _{DDA} off, V _{BAT} = 1.8 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving	_	1.0	_	μΑ
		V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving	_	1.1	_	μΑ
		V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving	_	0.9	_	μΑ
		V _{DD} off, V _{DDA} off, V _{BAT} = 2.6 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving	_	0.8	_	μΑ
		V _{DD} off, V _{DDA} off, V _{BAT} = 1.8 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving	_	0.7	_	μΑ
		V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Low driving	_	1.0	_	μΑ
		V_{DD} off, V_{DDA} off, V_{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low driving	_	0.9	_	μΑ
		V_{DD} off, V_{DDA} off, V_{BAT} = 2.6 V, LXTAL on with external crystal, RTC on, LXTAL Low driving	_	0.7	_	μΑ

Sym bol	Parameter	Conditions		Typ ⁽¹⁾	Max	Unit
		V_{DD} off, V_{DDA} off, V_{BAT} = 1.8 V, LXTAL on with external crystal, RTC on, LXTAL Low		0.6		μΑ
		driving				

- (1). Based on characterization, not tested in production.
- (2). Unless otherwise specified, all values given for $T_A = 25 \, ^{\circ}\text{C}$ and test result is mean value.
- (3). When System Clockisless than 4 MHz, an external source is used, and the HXTAL bypass function is needed, no PLL.
- (4). When System Clock is greater than 8 MHz, a crystal 8 MHz is used, and the HXTAL bypass function is closed, using PLL.
- (5). When analog peripheral blocks such as ADCs, DACs, HXTAL, LXTAL, IRC8M, or IRC40K are ON, an additional power consumption should be considered.

Figure 4-2. Typical supply current consumption in Run mode





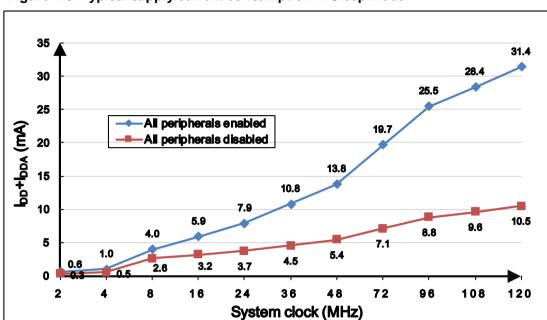


Figure 4-3. Typical supply current consumption in Sleep mode

Table 4-8. Peripheral current consumption characteristics(1)

	Peripherials ⁽⁴⁾	Typical consumption at $T_A = 25$ °C (TYP)	Unit
	DA C ⁽²⁾	0.81	
	PMU	1.41	
	BKP	1.93	
	CAN1	1.39	
	CA NO	1.41	
	l2C1	1.23	
	12C0	1.21	
	UART4	1.24	
	UART3	1.25	
	USART2	1.23	
A DD 4	USART1	1.24	Л
APB1	SPI2	1.17	mA
	SPI1	1.23	
	WWDGT	1.13	
	TIMER13	1.47	
	TIMER12	1.44	
	TIMER11	1.47	
	TIMER6	1.14	
	TIMER5	1.12	
	TIMER4	1.52	
	TIMER3	2.25	
	TIMER2	2.23	



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	Peripherials ⁽⁴⁾	Typical consumption at $T_A = 25$ °C (TYP)	Unit
	TIMER1	2.25	
ADDAPB1	стс	1.13	
	TIMER10	2.25	
	TIMER9	2.23	
	TIMER8	2.24	
	USART0	2.15	
	TIMER7	2.66	
	SPI0	1.87	
	TIMERO	2.63	
APB2	ADC1 ⁽³⁾	0.8	
AFDZ	ADC0 ⁽³⁾	0.8	
	GPIOG	1.99	
	GPIOF	2	
	GPIOE	1.99	
	GPIOD	2	
	GPIOC	2	
	GPIOB	2	
	GPIOA	1.29	
	ENET	5.04	
	USBFS	3.58	
AHB	EXMC	2.59	
AND	CRC	1.81	
	DMA1	1.48	
	DMA 0	1.61	

- (1). Based on characterization, not tested in production.
- (2). DEN0 and DEN1 bits in the DAC_CTL register are set to 1, and the converted value set to 0x800.
- (3). system clock = f_{HCLK} = 120 Mhz, f_{APB1} = $f_{HCLK}/2$, f_{APB2} = f_{HCLK} , f_{ADCCLK} = $f_{APB2}/2$, ADON bit is set to 1.
- (4). If there is no other description, then HXTAL = 25 MHz, system clock = f_{HCLK} = 120 MHz, f_{APB1} = $f_{HCLK}/2$, f_{APB2} = f_{HCLK} .

4.4. EMC characteristics

EMS (electromagnetic susceptibility) includes ESD (Electrostatic discharge, positive and negative) and FTB (Burst of Fast Transient voltage, positive and negative) testing result is given in *Table 4-9. EMS characteristics*, based on the EMS levels and classes compliant with IEC 61000 series standard.



Table 4-9. EMS characteristics(1)

Symbol	Parameter	Conditions	Level/Class
	Voltage applied to all device pins to	$V_{DD} = 3.3 \text{ V}, T_A = 25 ^{\circ}\text{C}$	
V_{ESD}	induce a functional disturbance	LQFP144, f _{HCLK} = 120 MHz	3A
	induce a functional disturbance	conforms to IEC 61000-4-2	
	Fast transient voltage burst applied to	$V_{DD} = 3.3 \text{ V}, T_A = 25 ^{\circ}\text{C}$	
V_{FTB}	induce a functional disturbance through	LQFP144, f _{HCLK} = 120 MHz	4A
	100 pF on V_{DD} and V_{SS} pins	conforms to IEC 61000-4-4	

^{(1).} Based on characterization, not tested in production.

4.5. Power supply supervisor characteristics

Table 4-10. Power supply supervisor characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		LVDT<2:0> = 000(rising edge)	_	2.15		
		LVDT<2:0> = 000(falling edge)		2.04		
		LVDT<2:0> = 001(rising edge)	_	2.29	_	
		LVDT<2:0> = 001(falling edge)	_	2.19	_	
		LVDT<2:0> = 010(rising edge)	_	2.43	_	
		LVDT<2:0> = 010(falling edge)	_	2.33	_	
		LVDT<2:0> = 011(rising edge)	_	2.57	_	
V (1)	Low voltage Detector level selection	LVDT<2:0> = 011(falling edge)	_	2.47	_	V
V _{LVD} ⁽¹⁾		LVDT<2:0> = 100(rising edge)	_	2.71	_	V
		LVDT<2:0> = 100(falling edge)	_	2.6	_	
		LVDT<2:0> = 101(rising edge)	_	2.85	_	
		LVDT<2:0> = 101(falling edge)	_	2.74	_	
		LVDT<2:0> = 110(rising edge)		2.99		
		LVDT<2:0> = 110(falling edge)		2.89		
		LVDT<2:0> = 111(rising edge)	_	3.13	_	
		LVDT<2:0> = 111(falling edge)	_	3.03	_	
V _{LVDhyst} ⁽²⁾	LVD hystersis			100		mV
V _{POR} ⁽¹⁾	Power on reset threshold		_	2.34	_	V
V _{PDR} ⁽¹⁾	Pow er down reset threshold	_	_	1.82	_	V



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{PDRhyst} ⁽²⁾	PDR hysteresis		_	600		mV
t _{RSTTEMPO} ⁽²⁾	Reset temporization		_	2		ms

^{(1).} Based on characterization, not tested in production.

4.6. Electrical sensitivity

The device is strained in order to determine its performance in terms of electrical sensitivity. Electrostatic discharges (ESD) are applied directly to the pins of the sample. Static latch-up (LU) test is based on the two measurement methods.

Table 4-11. ESD characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{ESD(HBM)}	Electrostatic discharge	T _A =25 °C;			4000	W
	voltage (human body model)	JESD22-A114	_			V
V	Electrostatic discharge	T _A =25 °C;			000	
V _{ESD(CDM)}	voltage (charge device model)	JESD22-C101	_	_	800	V

^{(1).} Based on characterization, not tested in production.

Table 4-12. Static latch-up characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	l-test	T _A =25 °C; JESD78			±200	mΑ
LU	V _{supply} over voltage	TA=25 C, JESD76	_	_	5.4	V

^{(1).} Based on characterization, not tested in production.

4.7. External clock characteristics

Table 4-13. High speed external clock (HXTAL) generated from a crystal/ceramic

^{(2).} Guaranteed by design, not tested in production.



characteristics

Symbol	Param et er	Conditions	Min	Тур	Max	Unit
f _{HXTAL} (1)	Crystal or ceramic frequency	$2.6 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$	4	8	32	MHz
R _F ⁽²⁾	Feedback resistor	$V_{DD} = 3.3 \text{ V}$	_	400	_	kΩ
C _{HXTAL} (2) (3)	Recommended load capacitance on OSCIN and OSCOUT	Ι		20	30	pF
Ducy _(HXTAL) ⁽²⁾	Crystal or ceramic duty cycle		30	50	70	%
gm ⁽²⁾	Oscillator transconductance	Startup	_	25	_	mA/V
IDDHXTAL ⁽¹⁾	Crystal or ceramic operating current	$V_{DD} = 3.3 \text{ V}, f_{HCLK} =$ $f_{IRC8M} = 8 \text{ MHz}$ $T_A = 25 \text{ °C}$	ı	1.25		mA
tsuhxtal ⁽¹⁾	Crystal or ceramic startup time	$V_{DD} = 3.3 \text{ V}, f_{HCLK} =$ $f_{IRC8M} = 8 \text{ MHz}$ $T_A = 25 \text{ °C}$		1.8	_	ms

- $(1). \ Based \ on \ characterization, \ not \ tested \ in \ production.$
- (2). Guaranteed by design, not tested in production.
- (3). $C_{\text{HXTAL1}} = C_{\text{HXTAL2}} = 2^*(C_{\text{LOAD}} C_{\text{S}})$, For C_{HXTAL1} and C_{HXTAL2} , it is recommended matching capacitance on OSCIN and OSCOUT. For C_{LOAD} , it is crystal/ceramic load capacitance, provided by the crystal or ceramic manufacturer. For C_{S} , it is PCB and MCU pin stray capacitance.

Table 4-14. High speed external clock characteristics (HXTAL in bypass mode)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HXTAL_ext} (1)	External clock source or oscillator frequency	2.6 V ≤ V _{DD} ≤ 3.6 V	1		50	MHz
V _{HXTALH} ⁽²⁾	OSCIN input pin high level voltage	V _{DD} = 3.3 V	0.7 V _{DD}		V_{DD}	V
V _{HXTALL} ⁽²⁾	OSCIN input pin low level voltage	V DD = 3.3 V	V _{SS}		0.3 V _{DD}	V
t _{H/L(HXTAL)} (2)	OSCIN high or low time	_	5		_	ns
t _{R/F(HXTAL)} (2)	OSCIN rise or fall time	_		1	10	ns
C _{IN} ⁽²⁾	OSCIN input capacitance	_	_	5	_	pF
Ducy _(HXTAL) (2)	Duty cycle	_	40	_	60	%

^{(1).} Based on characterization, not tested in production.

Table 4-15. Low speed external clock (LXTAL) generated from a crystal/ceramic

^{(2).} Guaranteed by design, not tested in production.



characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LXTAL} ⁽¹⁾	Crystal or ceramic frequency	$V_{DD} = 3.3 \text{ V}$	_	32.768		kHz
C _{LXTAL} ⁽²⁾⁽³⁾	Recommended matching capacitance on OSC32IN and OSC32OUT		_	10	_	pF
Ducy _(LXTAL) ⁽²⁾	Crystal or ceramic duty cycle	rystal or ceramic duty cycle — —			70	%
		Low er driving capability		4		
a (2)	Oscillator transconductance	Medium low driving capability	ı	6		
gm ⁽²⁾		Medium high driving capability		12	1	µA/V
		Higher driving capability		18	_	
		LXTALDRI[1:0] = 00		0.7		
(1)	Crystal or ceramic operating	LXTALDRI[1:0] = 01		8.0		
Iddlxtal ⁽¹⁾	current	LXTALDRI[1:0] = 10		1.0		μA
		LXTALDRI[1:0] = 11		1.3		
t _{SULXTAL} ⁽¹⁾⁽⁴⁾	Crystal or ceramic startup time	_	_	1.8	_	s

- (1). Based on characterization, not tested in production.
- (2). Guaranteed by design, not tested in production.
- (3). $C_{LXTAL1} = C_{LXTAL2} = 2*(C_{LOAD} C_S)$, For C_{LXTAL1} and C_{LXTAL2} , it is recommended matching capacitance on OSC32IN and OSC32OUT. For C_{LOAD} , it is crystal/ceramic load capacitance, provided by the crystal or ceramic manufacturer. For C_S , it is PCB and MCU pin stray capacitance.
- (4). $t_{SULXTAL}$ is the startup time measured from the moment it is enabled (by software) to the 32.768 kHz oscillator stabilization flags is SET. This value varies significantly with the crystal manufacturer.

Table 4-16. Low speed external user clock characteristics (LXTAL in bypass mode)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LXTAL_ext} ⁽¹⁾	External clock source or oscillator frequency	V _{DD} = 3.3 V		32.768	1000	kHz
V _{LXTALH} (2)	OSC32IN input pin high level voltage	_	0.7 V _{DD}	l	V_{DD}	.,
V _{LXTALL} ⁽²⁾	OSC32IN input pin low level voltage	_	V _{SS}	l	0.3 V _{DD}	V
t _{H/L(LXTAL)} (2)	OSC32IN high or low time	_	450		_	
t _{R/F(LXTAL)} (2)	OSC32IN rise or fall time	_		1	50	ns
C _{IN} ⁽²⁾	OSC32IN input capacitance	_	_	5	_	pF
Ducy _(LXTAL) (2)	Duty cycle	_	30	50	70	%

- (1). Based on characterization, not tested in production.
- (2). Guaranteed by design, not tested in production.



4.8. Internal clock characteristics

Table 4-17. High speed internal clock (IRC8M) characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{IRC8M}	High Speed Internal Oscillator (IRC8M) frequency	$V_{DD} = V_{DDA} = 3.3 \text{ V}$		8	_	MHz
		$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $T_A = -40 \text{ °C} \sim +85 \text{ °C}^{(1)}$	-2.5		+2.5	%
ACC _{IRC8M}	IRC8M oscillator Frequency – accuracy, Factory-trimmed	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $T_{A} = 0 \text{ °C } \sim +85 \text{ °C}^{(1)}$	-1.8	_	+1.8	%
/ COIR Colvi		$V_{DD} = V_{DDA} = 3.3 \text{ V}, T_A = 25 ^{\circ}\text{C}$	-1.0	_	+1.0	%
	IRC8M oscillator Frequency accuracy, User trimming step ⁽¹⁾			0.5	_	%
Ducy _{IRC8M} ⁽²⁾	IRC8M oscillator duty cycle	$V_{DD} = V_{DDA} = 3.3 \text{ V}$	45	50	55	%
IDDAIRC8M ⁽¹⁾	IRC8M oscillator operating current	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $f_{HCLK} = f_{HXTAL_PLL} = 120 \text{ MHz}$		66	_	μΑ
tsuirc8M ⁽¹⁾	IRC8M oscillator startup time	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $f_{HCLK} = f_{HXTAL_PLL} = 120 \text{ MHz}$	_	5	_	μs

^{(1).} Based on characterization, not tested in production.

Table 4-18. Low speed internal clock (IRC40K) characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{IRC40K} ⁽¹⁾	Low Speed Internal oscillator (IRC40K) frequency	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $T_{A} = -40 \text{ °C} \sim +85 \text{ °C}$	20	40	45	kHz
IDDAIRC40K ⁽²⁾	IRC40K oscillator operating current	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $f_{HCLK} = f_{HXTAL_PLL} = 120 \text{ MHz}$ $T_A = 25 \text{ °C}$	_	0.4	_	μΑ
tsuirc40K ⁽²⁾	IRC40K oscillator startup time	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $f_{HCLK} = f_{HXTAL_PLL} = 120 \text{ MHz}$ $T_A = 25 \text{ °C}$		110	_	μs

^{(1).} Guaranteed by design, not tested in production.

^{(2).} Guaranteed by design, not tested in production.

^{(2).} Based on characterization, not tested in production.



Table 4-19. High speed internal clock (IRC48M) characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{IRC48M}	High Speed Internal Oscillator (IRC48M) frequency	V _{DD} = 3.3 V		48		MHz
		$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $T_A = -40 ^{\circ}\text{C} \sim +85 ^{\circ}\text{C}^{(1)}$	-4.0	_	+5.0	%
	IRC48M oscillator Frequency accuracy, Factory-trimmed	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $T_A = 0 ^{\circ}\text{C} \sim +85 ^{\circ}\text{C}^{(1)}$	-3.0	_	+3.0	%
ACCIRC48M		$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $T_A = 25 \text{ °C}$	-2.0	_	+2.0	%
	IRC48M oscillator Frequency accuracy, User trimming step ⁽¹⁾			0.12	1	%
D _{IRC48M} ⁽²⁾	IRC48M oscillator duty cycle	$V_{DD} = V_{DDA} = 3.3 \text{ V}$	45	50	55	%
IDDAIRC48M ⁽¹⁾	IRC48M oscillator operating current	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $f_{HCLK} = f_{HXTAL_PLL} = 120$ MHz	_	356	_	μΑ
tsuirc48M ⁽¹⁾	IRC48M oscillator startup time	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $f_{HCLK} = f_{HXTAL_PLL} = 120$ MHz	—	2.7		μs

^{(1).} Based on characterization, not tested in production.

4.9. PLL characteristics

Table 4-20. PLL characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{PLLIN} ⁽¹⁾	PLL input clock frequency		1	-	25	MHz
f _{PLLOUT}	PLL output clock frequency		16	_	120	MHz
f _{VCO}	PLL VCO output clock frequency	_	32	_	240	MHz
t _{LOCK} (2)	PLL lock time	_	_	_	300	μs
I _{DDA} ⁽¹⁾⁽³⁾	Current consumption on V_{DDA}	VCO freq = 240 MHz		680		μA
(1)(4)	Cycle to cycle Jitter (rms)	Custom shall		35		
Jitter _{PLL} ⁽¹⁾⁽⁴⁾	Cycle to cycle Jitter (peak to peak)	System clock	_	371		ps

 $^{(1). \} Based \ on \ characterization, \ not \ tested \ in \ production.$

^{(2).} Guaranteed by design, not tested in production.

^{(2).} Guaranteed by design, not tested in production.

^{(3).} System clock= IRC8M = 8 MHz, PLL clocksource = IRC8M/2 = 4 MHz, f_{PLLOUT} = 120 MHz.

^{(4).} Value given with main PLL running.



Table 4-21. PLL1 characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
f _{PLLIN} ⁽¹⁾	PLL input clock frequency		1	_	25	MHz		
f _{PLLOUT}	PLL output clock frequency		16	_	120	MHz		
fvco	PLL VCO output clock		32		200	MHz		
	frequency		32		200	IVII IZ		
t _{LOCK} (2)	PLL lock time		_	_	300	μs		
L(1)(3)	Current consumption on	VCO frog - 200 MHz		520				
I _{DDA} ⁽¹⁾⁽³⁾	V_{DDA}	VCO freq = 200 MHz		520		μΑ		
Jitter _{PLL} (1)(4)	Cycle to cycle Jitter	System clock	_	371	_	ps		

- (1). Based on characterization, not tested in production.
- (2). Guaranteed by design, not tested in production.
- (3). System clock= IRC8M = 8 MHz, PLL1 clocksource = IRC48M = 48 MHz, f_{PLLOUT} = 120 MHz.
- (4). Value given with main PLL running.

Table 4-22. PLL2 characteristics

Symbol	Parameter	Conditions		Тур	Max	Unit
f _{PLLIN} ⁽¹⁾	PLL input clock frequency		1	-	25	MHz
f _{PLLOUT}	PLL output clock frequency		16	_	120	MHz
f _{VCO}	PLL VCO output clock frequency	_	32	_	200	MHz
t _{LOCK} (2)	PLL lock time	_		_	300	μs
I _{DDA} ⁽¹⁾⁽³⁾	Current consumption on VDDA	VCO freq = 200 MHz	_	520		μΑ
Jitter _{PLL} (1)(4)	Cycle to cycle Jitter	System clock	_	371	_	ps

- (1). Based on characterization, not tested in production.
- (2). Guaranteed by design, not tested in production.
- (3). System clock= IRC8M = 8 MHz, PLL2 clocksource = IRC48M = 48 MHz, f_{PLLOUT} = 120 MHz.
- (4). Value given with main PLL running.

4.10. Memory characteristics

Table 4-23. Flash memory characteristics

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ ⁽¹⁾	Max ⁽²⁾	Unit
PEcyc	Number of guaranteed program /erase cycles before failure (Endurance)	T _A = -40 °C ~ +85 °C	100	ı	l	kcycle s
t _{RET}	Data retention time	_	_	20	1	years
t _{PROG}	Word programming time	$T_A = -40 ^{\circ}\text{C} \sim +85 ^{\circ}\text{C}$	_	37.5	86	μs
t _{ERASE}	Page erase time	T _A = -40 °C ~ +85 °C		45	200/300 ⁽³⁾	ms
tmerase(256K)	Mass erase time	$T_A = -40 ^{\circ}\text{C} \sim +85 ^{\circ}\text{C}$	_	1	4.8/8.0 ⁽⁴⁾	s
tmerase(512K)	Mass erase time	T _A = -40 °C ~ +85 °C	_	4	19.2/32 ⁽⁵⁾	s
t _{MERASE(1MB)}	Mass erase time	T _A = -40 °C ~ +85 °C	_	6	28.8/48 ⁽⁶⁾	S

- (1). Based on characterization, not tested in production.
- (2). Guaranteed by design, not tested in production.
- (3). Max value with <50K cyclesis200 ms and >50K & <100K cyclesis300 ms.



- (4). Max value with <50K cyclesis 4.8 s and >50K & <100K cyclesis 8.0 s.
- (5). Max value with <50K cyclesis 19.2 s and >50K & <100K cyclesis 32 s.
- (6). Max value with <50K cyclesis 28.8 s and >50K & <100K cyclesis 48 s.

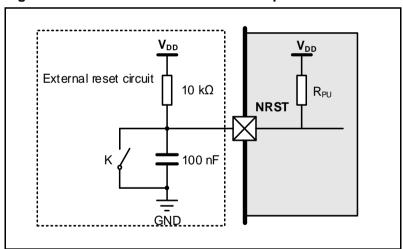
4.11. NRST pin characteristics

Table 4-24. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL(NRST)} ⁽¹⁾	NRST Input low level voltage		-0.5	_	0.3 V _{DD}	V
V _{IH(NRST)} ⁽¹⁾	NRST Input high level voltage	$V_{DD} = V_{DDA} = 2.6 \text{ V}$	0.7 V _{DD}	_	$V_{DD} + 0.5$	V
V _{hyst} (1)	Schmidt trigger Voltage hysteresis		_	390		mV
V _{IL(NRST)} ⁽¹⁾	NRST Input low level voltage		-0.5		0.3 V _{DD}	V
V _{IH(NRST)} ⁽¹⁾	NRST Input high level voltage	$V_{DD} = V_{DDA} = 3.3 \text{ V}$	0.7 V _{DD}	_	$V_{DD} + 0.5$	V
V _{hyst} (1)	Schmidt trigger Voltage hysteresis		_	410		mV
V _{IL(NRST)} ⁽¹⁾	NRST Input low level voltage		-0.5	_	0.3 V _{DD}	V
V _{IH(NRST)} ⁽¹⁾	NRST Input high level voltage V _{DD} = V _{DDA} = 3.6 V		0.7 V _{DD}	_	V _{DD} + 0.5	V
V _{hyst} ⁽¹⁾	Schmidt trigger Voltage hysteresis		_	430		mV
R _{pu} ⁽²⁾	Pull-up equivalent resistor	_	_	40		kΩ

- (1). Based on characterization, not tested in production.
- (2). Guaranteed by design, not tested in production.

Figure 4-4. Recommended external NRST pin circuit





4.12. **GPIO** characteristics

Table 4-25. I/O port DC characteristics(1) (3)

Symbol	Parame	ter	Conditions	Min	Тур	Max	Unit	
.,,	Standard IO Low voltage	•	$2.6 \text{ V} \le \text{V}_{DD} = \text{V}_{DDA} \le 3.6 \text{ V}$	_		0.3 V _{DD}	٧	
VIL	5V-tolerant IO Low level input voltage		2.6 V ≤ V _{DD} = V _{DDA} ≤ 3.6 V	_	1	0.3 V _{DD}	٧	
V _{IH}	Standard IO Low voltage	•	2.6 V ≤ V _{DD} = V _{DDA} ≤ 3.6 V	0.7 V _{DD}		_	V	
VIH	5V-tolerant IO input volt		$2.6 \text{ V} \le \text{V}_{DD} = \text{V}_{DDA} \le 3.6 \text{ V}$	0.7 V _{DD}			V	
	Low level outpo	ut voltage	$V_{DD} = 2.6V$	_		0.17		
VoL	for an IO Pin		$V_{DD} = 3.3 \text{ V}$			0.16	V	
	(I _{IO} = +8	mA)	$V_{DD} = 3.6V$	_	1	0.15		
	Low level outpo	ut voltage	$V_{DD} = 2.6V$			0.49		
V _{OL}	for an IO Pin		$V_{DD} = 3.3 V$	_		0.4	V	
	$(I_{10} = +20 \text{ mA})$		$V_{DD} = 3.6V$	_	_	0.34		
	High level outp	ut voltage	$V_{DD} = 2.6V$	2.4	_	_		
V_{OH}	for an IO	Pin	$V_{DD} = 3.3 \text{ V}$	3.15	_	_	V	
	(I _{IO} = +8	mA)	$V_{DD} = 3.6V$	3.44	_	_		
	High level outp	ut voltage	$V_{DD} = 2.6V$	2.02	_	_		
V _{OH}	for an IO	Pin	$V_{DD} = 3.3 \text{ V}$	2.8		_	V	
	(I _{IO} = +20	mA)	$V_{DD} = 3.6V$	3.15		_		
R _{PU} ⁽²⁾	Internal pull-up	All pins	$V_{IN} = V_{SS}$	30	40	50	kΩ	
K PU ¹⁻⁷	resistor	PA10		7.5	10	13.5	L/77	
R _{PD} ⁽²⁾	Internal pull-	All pins	$V_{IN} = V_{DD}$	30	40	50	kΩ	
KPD(-)	down resistor	PA10	_	7.5	10	13.5	N22	

^{(1).} Based on characterization, not tested in production.

Table 4-26. I/O port AC characteristics(1)(2)

GPIOx_MDy[1:0] bit value ⁽³⁾	Parameter	Conditions	Max	Unit
GPIOx_CTL->MDy[1:0]=10 (IO_Speed = 2MHz)	Marrian	$2.6 \le V_{DD} \le 3.6 \text{ V}, C_L = 10 \text{ pF}$	15	
	Maximum frequency ⁽⁴⁾	$2.6 \le V_{DD} \le 3.6 \text{ V}, C_L = 30 \text{ pF}$	10	MHz
		$2.6 \le V_{DD} \le 3.6 \text{ V}, C_L = 50 \text{ pF}$	8	
CDOV CTL - MDv[4:0] 04	Maximum	$2.6 \le V_{DD} \le 3.6 \text{ V}, C_L = 10 \text{ pF}$	50	
GPIOx_CTL->MDy[1:0] = 01 (IO_Speed = 10MHz)	Maximum frequency ⁽⁴⁾	$2.6 \le V_{DD} \le 3.6 \text{ V}, C_L = 30 \text{ pF}$	25	MHz
		$2.6 \le V_{DD} \le 3.6 \text{ V}, C_L = 50 \text{ pF}$	15	
GPIOx_CTL->MDy[1:0]=11	Maximum	$2.6 \le V_{DD} \le 3.6 \text{ V}, C_L = 10 \text{ pF}$	100	MHz

^{(2).} Guaranteed by design, not tested in production.

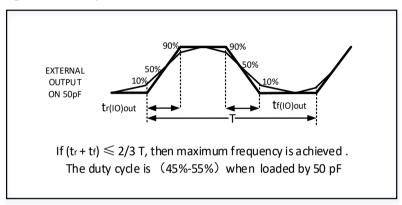
^{(3).} All pins except PC13 / PC14 / PC15. Since PC13 to PC15 are supplied through the Power Switch, which can only be obtained by a small current, the speed of GPIOs PC13 to PC15 should not exceed 2 MHz when they are in output mode(maximumload: 30 pF).



GPIOx_MDy[1:0] bit value ⁽³⁾	Parameter	Conditions	Max	Unit
(IO_Speed = 50MHz)	frequency ⁽⁴⁾	$2.6 \le V_{DD} \le 3.6 \text{ V}, C_L = 30 \text{ pF}$	70	
		$2.6 \le V_{DD} \le 3.6 \text{ V}, C_L = 50 \text{ pF}$	50	
GPIOx_CTL->MDy[1:0]=11 and	Maximum	$2.6 \le V_{DD} \le 3.6 \text{ V}, C_L = 10 \text{ pF}$	120	
GPIOx_SPDy=1		$2.6 \le V_{DD} \le 3.6 \text{ V}, C_L = 30 \text{ pF}$	100	MHz
(IO_Speed = MAX)	frequency ⁽⁴⁾	$2.6 \le V_{DD} \le 3.6 \text{ V}, C_L = 50 \text{ pF}$	60	

- (1). Based on characterization, not tested in production.
- (2). Unless otherwise specified, all test results given for $T_A = 25$ °C.
- (3). The I/O speed is configured using the GPIOx_CTL-> MDy[1:0] bits. Refer to the GD32F 30x user manual which is selected to set the GPIO port output speed.
- (4). The maximum frequency is defined in Figure 4-5, and maximum frequency cannot exceed 120 MHz.

Figure 4-5. I/O port AC characteristics definition



4.13. Temperature sensor characteristics

Table 4-27. Temperature sensor characteristics⁽¹⁾

Symbol	Parameter	Min	Тур	Max	Unit
TL	VSENSE linearity with temperature	1	±1.5		°C
Avg_Slope	Average slope	1	4.1		mV/°C
V ₂₅	Voltage at 25 ℃	_	1.45	_	V
t _{S_temp} (2)	ADC sampling time when reading the temperature	-	17.1		μs

- (1). Based on characterization, not tested in production.
- (2). Shortest sampling time can be determined in the application by multiple iterations.

4.14. ADC characteristics

Table 4-28. ADC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DDA}^{(1)}$	Operating voltage	ı	2.6	3.3	3.6	V
V _{IN} ⁽¹⁾	ADC input voltage range	ı	0	_	V_{REF}	V
V _{REF+} ⁽²⁾	Positive Reference Voltage	_	2.4	_	V_{DDA}	V
V (2)	Negative Reference			\/·		V
V _{REF-} ⁽²⁾	Voltage	_	_	V _{SSA}	_	V

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{ADC} ⁽¹⁾	ADC clock	_	0.1	_	40	MHz
		12-bit	0.007	_	2.86	
fs ⁽¹⁾	Compling rate	10-bit	0.008	_	3.33	MSP
IS'''	Sampling rate	8-bit	0.01	_	4	S
		6-bit	0.012	_	5	
V _{AIN} ⁽¹⁾	Analog input voltage	16 external; 2 internal	0	_	V_{DDA}	V
R _{AIN} ⁽²⁾	External input impedance	See Equation 1	_	_	32.9	kΩ
R _{ADC} ⁽²⁾	Input sampling switch resistance	_	_	_	0.55	kΩ
C _{ADC} ⁽²⁾	Input sampling capacitance	No pin/pad capacitance included			5.5	pF
t _{CAL} ⁽²⁾	Calibration time	$f_{ADC} = 40 \text{ MHz}$	_	3.275	_	μs
t _s (2)	Sampling time	$f_{ADC} = 40 \text{ MHz}$	0.0375	_	5.99	μs
	.	12-bit	_	14	_	
. (2)	Total conversion	10-bit	_	12	_	1/
t _{CONV} ⁽²⁾	time(including sampling	8-bit	_	10	_	f _{ADC}
	time)	6-bit	_	8	_	
t _{SU} (2)	Startup time	_	_	_	1	μS

^{(1).} Based on characterization, not tested in production.

$$\textit{Equation 1:} \, \mathsf{R}_{\mathsf{AIN}} \,\, \mathsf{max} \,\, \mathsf{formula} \,\, R_{\mathsf{AIN}} < \frac{\mathsf{T_S}}{\mathsf{f}_{\mathsf{ADC}^*}\mathsf{C}_{\mathsf{ADC}^*}\!\!\ln(2^{\mathsf{N}+2})} - \, R_{\mathsf{ADC}}$$

The formula above (Equation 1) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 4-29. ADC $R_{AIN max}$ for $f_{ADC} = 40 MHz$

T _s (cycles)	t _s (μs)	R _{AIN max} (kΩ)
1.5	0.0375	0.15
7.5	0.1875	2.96
13.5	0.3375	5.77
28.5	0.7125	12.8
41.5	1.0375	18.9
55.5	1.3875	25.4
71.5	1.7875	32.9
239.5	5.9875	N/A

Table 4-30. ADC dynamic accuracy at $f_{ADC} = 14 \text{ MHz}^{(1)}$

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit		
ENOB	Effective number of bits	f _{ADC} = 14 MHz	_	10.8		bits		
SNDR	Signal-to-noise and distortion ratio	$V_{DDA} = V_{REF+} = 3.3 \text{ V}$	_	66.7				
SNR	Signal-to-noise ratio	Input Frequency = 20 kHz	_	67.4	_	dB		
THD	Total harmonic distortion	Temperature = 25 °C	_	-76.3	_			

^{(1).} Based on characterization, not tested in production.

^{(2).} Guaranteed by design, not tested in production.



Table 4-31. ADC dynamic accuracy at f_{ADC} = 40 MHz⁽¹⁾

Symbol	Parameter Parameter	Test conditions	Min	Тур	Max	Unit
ENOB	Effective number of bits	f _{ADC} = 40 MHz		10		bits
SNDR	Signal-to-noise and distortion ratio	$V_{DDA} = V_{REF+} = 3.3 \text{ V}$		62		
SNR	Signal-to-noise ratio	Input Frequency = 20 kHz	_	62.2	_	dB
THD	Total harmonic distortion	Temperature = 25 °C	_	-68.6	_	

^{(1).} Based on characterization, not tested in production.

Table 4-32. ADC static accuracy at f_{ADC} = 14 MHz⁽¹⁾

Symbol	Parameter	Test conditions	Тур	Max	Unit
Offset	Offset error	f	±1	_	
DNL	Differential linearity error	f _{ADC} = 14 MHz V _{DDA} = V _{REF+} = 3.3 V	±0.9	_	LSB
INL	Integral linearity error	V DDA = V REF+ = 3.3 V	±1	_	

^{(1).} Based on characterization, not tested in production.

4.15. DAC characteristics

Table 4-33. DAC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DDA} ⁽¹⁾	Operating voltage	_	2.6	3.3	3.6	V
V _{REF+} ⁽²⁾	Positive Reference Voltage	_	2.4	_	V_{DDA}	٧
V _{REF-} (2)	Negative Reference Voltage	_		V _{SSA}		V
R _{LOAD} ⁽²⁾	Load resistance	Resistive load with buffer ON	5			kΩ
Ro ⁽²⁾	Impedance output with buffer OFF	_			15	kΩ
C _{LOAD} ⁽²⁾	Load capacitance	No pin/pad capacitance included			50	pF
DA C_OUT min ⁽²⁾	Low er DAC_OUT voltage with buffer ON	_	0.2	_	-	V
DAC_OUT max ⁽²⁾	Higher DAC_OUT voltage with buffer ON	_	_	_	V _{DDA} -	٧
DA C_OUT min ⁽²⁾	Low er DAC_OUT voltage with buffer OFF	_	_	0.5	1	mV
DAC_OUT max ⁽²⁾	Higher DAC_OUT voltage with buffer OFF				V _{DDA} - 1LSB	V
I _{DDA} ⁽¹⁾	DAC current consumption	With no load, middle code(0x800) on the input, $V_{REF+} = 3.6 \text{ V}$		470	ı	uA
IDDA` /	in quiescent mode	With no load, worst code(0xF1C) on the input, $V_{REF+} = 3.6 \text{ V}$	_	500	_	uA
IDDVREF+ ⁽¹⁾	DAC current consumption in quiescent mode	With no load, middle code(0x800) on the input, $V_{REF+} = 3.6 \text{ V}$	_	86	_	uA



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		With no load, worst code(0xF1C)		298		uA
		on the input, $V_{REF+} = 3.6 \text{ V}$		290		uA
DNL ⁽¹⁾	Differential non-linearity	DAC in 12-bit mode			±3	LSB
DINL	error DAC in 12-bit mode		_	_	7	LOD
INL ⁽¹⁾	Integral non-linearity	DAC in 12-bit mode	_	_	±4	LSB
Offset ⁽¹⁾	Offset error	DAC in 12-bit mode	_	_	±12	LSB
GE ⁽¹⁾	Gain error	DAC in 12-bit mode	_	_	±0.5	%
T _{setting} (1)	Settling time	$C_{LOAD} \leqslant 50$ pF, $R_{LOAD} \geqslant 5$ k Ω	_	0.3	1	μs
T _{wakeup} (2)	Wakeup from off state	_	_	5	10	μs
	Max frequency for a					
Update	correct DAC_OUT	Co. 50 pE Do. 5 Fk0			4	MC/a
rate ⁽²⁾	change from code i to	$C_{LOAD} \leqslant 50 \text{ pF, } R_{LOAD} \geqslant 5 \text{ k}\Omega$	_	_	4	MS/s
	i±1LSBs					
	Pow er supply rejection					
PSRR ⁽²⁾	ratio	_	55	80	_	dB
	(to V _{DDA})					

^{(1).} Based on characterization, not tested in production.

4.16. I2C characteristics

Table 4-34. I2C characteristics(1)(2)(3)

Symbol	Parameter	Conditio	Standard	d mode	Fast n	node	Fast plu	mode us	Unit
		ns	Min	Max	Min	Max	Min	Max	
t _{SCL(H)}	SCL clock high time		4.0	_	0.6	_	0.2		μs
t _{SCL(L)}	SCL clock low time		4.7	_	1.3	_	0.5	1	μs
t _{su(SDA)}	SDA setup time		2	-	0.8		0.1	1	ns
t _{h(SDA)}	SDA data hold time	_	250	_	250	_	130		ns
t _r (SDA/SCL)	SDA and SCL rise time	_	_	1000	20	300		120	ns
t _f (SDA/SCL)	SDA and SCL fall time	_	4	300	4	300	4	120	ns
t _{h(STA)}	Start condition hold time	_	4.0		0.6	_	0.26	_	μs

 $^{(1). \} Guaranteed \ by \ design, \ not \ tested \ in \ production.$

^{(2).} Guaranteed by design, not tested in production.

^{(2).} To ensure the standard mode I2C frequency, f_{PCLK1} must be at least 2 MHz, To ensure the fast mode I2C frequency, f_{PCLK1} must be at least 4 MHz. To ensure the fast mode plus I2C frequency, f_{PCLK1} must be at least a multiple of 10 MHz.

^{(3).} The device should provide a data hold time of 300 ns at least in order to bridge the undefined region of the falling edge of SCL.



4.17. SPI characteristics

Table 4-35. Standard SPI characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{SCK}	SCK clock frequency	_	_	_	30	MHz
t _{SCK(H)}	SCK clock high time	Master mode, f _{PCLKx} = 120 MHz, presc = 8		33.33	34.83	ns
t _{SCK(L)}	SCK clock low time	Master mode, $f_{PCLKx} = 120 \text{ MHz}$, $presc = 8$	31.83	33.33	34.83	ns
		SPI master mode				
t _{V(MO)}	Data output valid time	_	_	5	6	ns
t _{H(MO)}	Data output hold time	_	3	_	_	ns
t _{SU(MI)}	Data input setup time	_	1	_	_	ns
t _{H(MI)}	Data input hold time	_	0	_	_	ns
		SPI slave mode				
tsu(NSS)	NSS enable setup time	_	0	_	_	ns
t _{H(NSS)}	NSS enable hold time	_	1	_	_	ns
t _{A(SO)}	Data output access time	_	5	_	9	ns
t _{DIS(SO)}	Data output disable time	_	6	_	10	ns
t _{V(SO)}	Data output valid time	_		10	12	ns
t _{H(SO)}	Data output hold time	_	8			ns
t _{SU(SI)}	Data input setup time		0	_	_	ns
t _{H(SI)}	Data input hold time	_	1	_	_	ns

^{(1).} Based on characterization, not tested in production.



4.18. I2S characteristics

Table 4-36. I2S characteristics(1)(2)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		Master mode (data: 16 bits,	0.075	0.077	3.079	
fcĸ	Clock frequency	Audio frequency = 96 kHz)	3.075	3.077		MHz
		Slave mode	0	_	10	
t _H	Clock high time		162	_	_	ns
tL	Clock low time	_	163	_	_	ns
t _{V(WS)}	WS valid time	Master mode	0	_	_	ns
t _{H(WS)}	WS hold time	Master mode	0	_	_	ns
tsu(ws)	WS setup time	Slave mode	0	_	_	ns
t _{H(WS)}	WS hold time	Slave mode	2	_	_	ns
	I2S slave input clock duty	01 1		50	_	0.4
Ducy _(SCK)	cycle	Slave mode				%
tsu(sd_mr)	Data input setup time	Master mode	1	_	_	ns
t _{su(SD_SR)}	Data input setup time	Slave mode	0	_	_	ns
t _{H(SD_MR)}	Data input hald time	Master receiver	0	_	_	ns
t _{H(SD_SR)}	Data input hold time	Slave receiver	1	_	_	ns
	Data autout valid time	Slave transmitter			40	
t _V (SD_ST)	Data output valid time	(after enable edge)		_	12	ns
t. ()	Data output hold time	Slave transmitter	7			ns
t _{h(SD_ST)}	Data output noid time	(after enable edge)	,			115
t (00 14=	Data output valid time	Master transmitter	_		6	nc
t _v (SD_MT)	Data output valid time	(after enable edge)			Ö	ns
t	Data output hold time	Master transmitter	_			
t _{h(SD_MT)}	Data output hold time	(after enable edge)	2		_	ns

^{(1).} Guaranteed by design, not tested in production.

4.19. USART characteristics

Table 4-37. USART characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
fsck	SCK clock frequency	$f_{PCLKx} = 120 \text{ MHz}$	_	-	60	MHz
tsck(H)	SCK clock high time	$f_{PCLKx} = 120 \text{ MHz}$	7.5	_	_	ns
t _{SCK(L)}	SCK clock low time	f _{PCLKx} = 120 MHz	7.5		_	ns

^{(1).} Guaranteed by design, not tested in production.

^{(2).} Based on characterization, not tested in production



4.20. CAN characteristics

Refer to <u>Table 4-25. I/O port DC characteristics</u>(1) for more details on the input/output alternate function characteristics (CANTX and CANRX).

4.21. USBFS characteristics

Table 4-38. USBFS start up time

Symbol	Parameter	Max	Unit
tstartup ⁽¹⁾	USBFS startup time	1	μs

^{(1).} Guaranteed by design, not tested in production.

Table 4-39. USBFS DC electrical characteristics

Symb	ol	Parameter	Conditions	Min	Тур	Max	Unit
	V_{DD}	USBFS operating voltage	_	3	_	3.6	
	V_{DI}	Differential input sensitivity		0.2	_	_	
Input levels ⁽¹⁾	V _{СМ}	Differential common mode range	Includes V _{DI} range	0.8	_	2.5	V
	V_{SE}	Single ended receiver threshold	Ι	1.3	—	2.0	
Output	V_{OL}	Static output level low	R_L of 1.0 $k\Omega$ to 3.6 V	_	0.064	0.3	٧
levels (2)	VoH	Static output level high	R_L of 15 $k\Omega$ to VSS	2.8	3.3	3.6	V
R _{PD} ⁽²	2)	PA11, PA12(USB_DM/DP)	VIN = VDD	17	20.574	24	
KPD/-	,	PA9(USB_VBUS)	V IN = V DD	0.65	_	2.0	kΩ
R _{PU} ⁽²	2)	PA11, PA12(USB_DM/DP)		1.5	1.585	2.1	K12
KPU\-	,	PA9(USB_VBUS)	$V_{IN} = V_{SS}$	0.25	0.326	0.55	

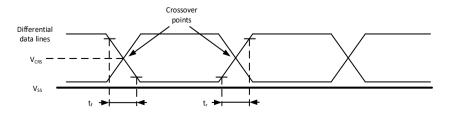
^{(1).} Guaranteed by design, not tested in production.

Table 4-40. USBFS full speed-electrical characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _R	Rise time	CL = 50 pF	4		20	ns
t _F	Fall time	CL = 50 pF	4		20	ns
t _{RFM}	Rise/fall time matching	t _R / t _F	90		110	%
VCRS	Output signal crossover voltage	_	1.3	_	2.0	V

^{(1).} Guaranteed by design, not tested in production.

Figure 4-6. USBFS timings: definition of data signal rise and fall time



^{(2).} Based on characterization, not tested in production.



4.22. EXMC characteristics

Table 4-41. Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings (1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
t _{w(NE)}	EXMC_NE low time	40.5	42.5	ns
tv(NOE_NE)	EXMC_NEx low to EXMC_NOE low	0	_	ns
t _{w(NOE)}	EXMC_NOE low time	40.5	42.5	ns
t _{h(NE_NOE)}	EXMC_NOE high to EXMC_NE high hold time	0	_	ns
t _{v(A_NE)}	EXMC_NEx low to EXMC_A valid	0	_	ns
t _{v(BL_NE)}	EXMC_NEx low to EXMC_BL valid	0	_	ns
t _{su(DATA_NE)}	Data to EXMC_NEx high setup time	32.2	_	ns
t _{su(DATA_NOE)}	Data to EXMC_NOEx high setup time	32.2	_	ns
t _{h(DATA_NOE)}	Data hold time after EXMC_NOE high	0	_	ns
t _{h(DATA_NE)}	Data hold time after EXMC_NEx high	0	_	ns
t _{v(NADV_NE)}	EXMC_NEx low to EXMC_NADV low	0	_	ns
t _{w(NADV)}	EXMC_NA DV low time	7.3	9.3	ns

^{(1).} $C_L = 30 pF$.

Table 4-42. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings (1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
t _{w(NE)}	EXMC_NE low time	23.9	25.9	ns
t _{V(NWE_NE)}	EXMC_NEx low to EXMC_NWE low	7.3	_	ns
t _{w(NWE)}	EXMC_NWE low time	7.3	9.3	ns
t _{h(NE_NWE)}	EXMC_NWE high to EXMC_NE high hold time	7.3	9.3	ns
t _{v(A_NE)}	EXMC_NEx low to EXMC_A valid	0	1	ns
tv(nadv_ne)	EXMC_NEx low to EXMC_NADV low	0		ns
t _{w(NADV)}	EXMC_NA DV low time	7.3	9.3	ns
t _{h(AD_NADV)}	EXMC_AD(address) valid hold time after EXMC_NADV high	15.6	I	ns
t _{h(A_NWE)}	Address hold time after EXMC_NWE high	7.3	1	ns
t _{h(BL_NWE)}	EXMC_BL hold time after EXMC_NWE high	7.3		ns
t _{v(BL_NE)}	EXMC_NEx low to EXMC_BL valid	23.9	25.9	ns
t _{v(DATA_NADV)}	EXMC_NA DV high to DATA valid	7.3	_	ns
t _{h(DATA_NWE)}	Data hold time after EXMC_NWE high	7.3	9.3	ns

^{(1).} $C_L = 30 pF$.

^{(2).} Guaranteed by design, not tested in production.

^{(3).} Based on characterization, not tested in production.

^{(4).} Based on configure: $f_{HCLK} = 120 \text{ MHz}$, AddressSetupTime = 0, AddressHoldTime = 1, DataSetupTime = 1.

^{(2).} Guaranteed by design, not tested in production.

^{(3).} Based on characterization, not tested in production.

^{(4).} Based on configure: f_{HCLK} = 120 MHz, AddressSetupTime = 0, AddressHoldTime = 1, DataSetupTime = 1.



Table 4-43. Asynchronous multiplexed PSRAM/NOR read timings (1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
t _{w(NE)}	EXMC_NE low time	57.1	59.1	ns
tv(NOE_NE)	EXMC_NEx low to EXMC_NOE low	23.9	_	ns
t _{w(NOE)}	EXMC_NOE low time	32.2	34.2	ns
th(NE_NOE)	EXMC_NOE high to EXMC_NE high hold time	0	_	ns
t _{v(A_NE)}	EXMC_NEx low to EXMC_A valid	0	_	ns
t _{v(A_NOE)}	Address hold time after EXMC_NOE high	0	_	ns
t _{v(BL_NE)}	EXMC_NEx low to EXMC_BL valid	0	_	ns
t _{h(BL_NOE)}	EXMC_BL hold time after EXMC_NOE high	0	_	ns
t _{su(DATA_NE)}	Data to EXMC_NEx high setup time	33.2	_	ns
t _{su(DATA_NOE)}	Data to EXMC_NOEx high setup time	33.2	_	ns
t _{h(DATA_NOE)}	Data hold time after EXMC_NOE high	0	_	ns
t _{h(DATA_NE)}	Data hold time after EXMC_NEx high	0	_	ns
t _{v(NADV_NE)}	EXMC_NEx low to EXMC_NADV low	0	_	ns
t _{w(NADV)}	EXMC_NA DV low time	7.3	9.3	ns
T _{h(AD_NADV)}	EXMC_AD(adress) valid hold time after EXMC_NADV high	7.3	9.3	ns

^{(1).} $C_L = 30 \text{ pF}.$

- (2). Guaranteed by design, not tested in production.
- (3). Based on characterization, not tested in production.
- (4). Based on configure: $f_{HCLK} = 120 \text{ MHz}$, AddressSetupTime = 0, AddressHoldTime = 1, DataSetupTime = 1.

Table 4-44. Asynchronous multiplexed PSRAM/NOR write timings (1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
t _{w(NE)}	EXMC_NE low time	40.5	42.5	ns
t _{V(NWE_NE)}	EXMC_NEx low to EXMC_NWE low	7.3	1	ns
t _{w(NWE)}	EXMC_NWE low time	23.9	25.9	ns
t _{h(NE_NWE)}	EXMC_NWE high to EXMC_NE high hold time	7.3		ns
t _{v(A_NE)}	EXMC_NEx low to EXMC_A valid	0	_	ns
t _{V(NADV_NE)}	EXMC_NEx low to EXMC_NADV low	0	_	ns
t _{w(NADV)}	EXMC_NA DV low time	7.3	9.3	ns
t _{h(AD_NADV)}	EXMC_AD(address) valid hold time after EXMC_NADV high	7.3	_	ns
t _{h(A_NWE)}	Address hold time after EXMC_NWE high	7.3	_	ns
t _{h(BL_NWE)}	EXMC_BL hold time after EXMC_NWE high	7.3	_	ns
t _{v(BL_NE)}	EXMC_NEx low to EXMC_BL valid	0	_	ns
t _{v(DATA_NADV)}	EXMC_NA DV high to DATA valid	7.3	_	ns
t _{h(DATA_NWE)}	Data hold time after EXMC_NWE high	7.3	_	ns

^{(1).} $C_L = 30 pF$.

- (2). Guaranteed by design, not tested in production.
- (3). Based on characterization, not tested in production.
- $(4). \ Based \ on \ configure: f_{HCLK} = 120 \ MHz, \ AddressSetupTime = 0, \ AddressHoldTime = 1, \ DataSetupTime = 1.$



Table 4-45. Synchronous multiplexed PSRAM/NOR read timings (1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
t _{w(CLK)}	EXMC_CLK period	33.2	_	ns
t _{d(CLKL-NExL)}	EXMC_CLK low to EXMC_NEx low	0	_	ns
t _{d(CLKH-NExH)}	EXMC_CLK high to EXMC_NEx high	15.6	1	ns
t _{d(CLKL-NADVL)}	EXMC_CLK low to EXMC_NA DV low	0	1	ns
t _{d(CLKL-NADVH)}	EXMC_CLK low to EXMC_NA DV high	0		ns
t _{d(CLKL-AV)}	EXMC_CLK low to EXMC_Ax valid	0		ns
t _{d(CLKH-AIV)}	EXMC_CLK high to EXMC_Ax invalid	15.6		ns
t _{d(CLKL-NOEL)}	EXMC_CLK low to EXMC_NOE low	0	ı	ns
t _{d(CLKH-NOEH)}	EXMC_CLK high to EXMC_NOE high	15.6	ı	ns
t _{d(CLKL-ADV)}	EXMC_CLK low to EXMC_AD valid	0	_	ns
t _{d(CLKL-ADIV)}	EXMC_CLK low to EXMC_AD invalid	0	_	ns

- (1). $C_L = 30 pF$.
- (2). Guaranteed by design, not tested in production.
- $(3). \ Based \ on \ characterization, \ not \ tested \ in \ production.$
- (4). Based on configure: f_{HCLK} = 120 MHz, BurstAccessMode = Enable; Memory Type = PSRAM; WriteBurst=Enable; CLKDivision = 3 (EXMC_CLK is 4 divided by HCLK); Data Latency = 1.

Table 4-46. Synchronous multiplexed PSRAM write timings (1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
t _{w(CLK)}	EXMC_CLK period	33.2		ns
t _{d(CLKL-NExL)}	EXMC_CLK low to EXMC_NEx low	0		ns
t _{d(CLKH-NExH)}	EXMC_CLK high to EXMC_NEx high	15.6		ns
t _{d(CLKL-NADVL)}	EXMC_CLK low to EXMC_NA DV low	0	ı	ns
t _{d(CLKL-NADVH)}	EXMC_CLK low to EXMC_NA DV high	0	_	ns
t _{d(CLKL-AV)}	EXMC_CLK low to EXMC_Ax valid	0	ı	ns
t _{d(CLKH-AIV)}	EXMC_CLK high to EXMC_Ax invalid	15.6	ı	ns
t _{d(CLKL-NWEL)}	EXMC_CLK low to EXMC_NWE low	0	1	ns
t _{d(CLKH-NWEH)}	EXMC_CLK high to EXMC_NWE high	15.6		ns
t _{d(CLKL-ADIV)}	EXMC_CLK low to EXMC_AD invalid	0		ns
t _{d(CLKL-DATA)}	EXMC_A/D valid data after EXMC_CLK low	0	_	ns
t _{h(CLKL-NBLH)}	EXMC_CLK low to EXMC_NBL high	0	_	ns

- (1). $C_L = 30 pF$.
- (2). Guaranteed by design, not tested in production.
- (3). Based on characterization, not tested in production.
- (4). Based on configure: f_{HCLK} = 120 MHz, BurstAccessMode = Enable; MemoryType = PSRAM; WriteBurst = Enable; CLKDivision = 3 (EXMC_CLK is 4 divided by HCLK); DataLatency = 1.



Table 4-47. Synchronous non-multiplexed PSRAM/NOR read timings (1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
t _{w(CLK)}	EXMC_CLK period	33.2	_	ns
t _{d(CLKL-NExL)}	EXMC_CLK low to EXMC_NEx low	0	_	ns
t _{d(CLKH-NExH)}	EXMC_CLK high to EXMC_NEx high	15.6	_	ns
t _{d(CLKL-NADVL)}	EXMC_CLK low to EXMC_NA DV low	0	_	ns
t _{d(CLKL-NADVH)}	EXMC_CLK low to EXMC_NA DV high	0	_	ns
t _{d(CLKL-AV)}	EXMC_CLK low to EXMC_Ax valid	0	_	ns
t _{d(CLKH-AIV)}	EXMC_CLK high to EXMC_Ax invalid	15.6	_	ns
t _{d(CLKL-NOEL)}	EXMC_CLK low to EXMC_NOE low	0	_	ns
t _{d(CLKH-NOEH)}	EXMC_CLK high to EXMC_NOE high	15.6	_	ns

- (1). $C_L = 30 \, \overline{pF}$.
- (2). Guaranteed by design, not tested in production.
- (3). Based on characterization, not tested in production.
- (4). Based on configure: HCLK=120 MHz, BurstAccessMode = Enable; MemoryType = PSRAM; WriteBurst = Enable; CLKDivision = 3 (EXMC_CLK is 4 divided by HCLK); DataLatency = 1.

Table 4-48. Synchronous non-multiplexed PSRAM write timings (1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
t _{w(CLK)}	EXMC_CLK period	33.2	ı	ns
t _{d(CLKL-NExL)}	EXMC_CLK low to EXMC_NEx low	0	1	ns
t _{d(CLKH-NExH)}	EXMC_CLK high to EXMC_NEx high	15.6		ns
t _{d(CLKL-NADVL)}	EXMC_CLK low to EXMC_NA DV low	0	_	ns
t _{d(CLKL-NADVH)}	EXMC_CLK low to EXMC_NA DV high	0		ns
t _{d(CLKL-AV)}	EXMC_CLK low to EXMC_Ax valid	0		ns
t _{d(CLKH-AIV)}	EXMC_CLK high to EXMC_Ax invalid	15.6	_	ns
t _{d(CLKL-NWEL)}	EXMC_CLK low to EXMC_NWE low	0	_	ns
t _d (CLKH-NWEH)	EXMC_CLK high to EXMC_NWE high	15.6	_	ns
t _{d(CLKL-DATA)}	EXMC_A/D valid data after EXMC_CLK low	0	_	ns
t _{h(CLKL-NBLH)}	EXMC_CLK low to EXMC_NBL high	0	_	ns

- (1). $C_L = 30 pF$.
- (2). Guaranteed by design, not tested in production.
- (3). Based on characterization, not tested in production.
- (4). Based on configure: HCLK = 120 MHz, BurstAccessMode = Enable; MemoryType = PSRAM; WriteBurst = Enable; CLKDivision = 3 (EXMC_CLK is 4 divided by HCLK); DataLatency = 1.



4.23. TIMER characteristics

Table 4-49. TIMER characteristics (1)

Symbol	Parameter	Conditions	Min	Max	Unit
	Timer resolution time		1		t _{TIMERxCLK}
t _{res}	Timer resolution time	f _{TIMERxCLK} = 120 MHz	8.4		ns
	Times automod alsoli francisco		0	f _{TIMERxCLK} /2	MHz
f _{EXT}	Timer external clock frequency	- 1 — ftimerxclk = 120 MHz 8.4 — 0 ftimerxclk/2	MHz		
RES	Timer resolution		_	16	bit
4	16-bit counter clock period		1	65536	t _{TIMERxCLK}
tCOUNTER	w hen internal clock is selected	f _{TIMERxCLK} = 120 MHz	0.0084	546	μs
t	Maximum, pagaible count	_	_	65536x65536	t _{TIMERxCLK}
tmax_count	Maximum possible count	f _{TIMERxCLK} = 120 MHz	_	35.7	S

^{(1).} Guaranteed by design, not tested in production.

4.24. WDGT characteristics

Table 4-50. FWDGT min/max timeout period at 40 kHz (IRC40K) (1)

Prescaler divider	PR[2:0] bits	Min timeout RLD[11:0] = 0x000	Max timeout RLD[11:0] = 0xFFF	Unit
1/4	000	0.1	409.6	
1/8	001	0.2	819.2	
1/16	010	0.4	1638.4	
1/32	011	0.8	3276.8	ms
1/64	100	1.6	6553.6	
1/128	101	3.2	13107.2	
1/256	110 or 111	6.4	26214.4	

^{(1).} Guaranteed by design, not tested in production.

Table 4-51. WWDGT min-max timeout value at 60 MHz (f_{PCLK1})⁽¹⁾

Prescaler divider	PSC[2:0]	Min timeout value CNT[6:0] = 0x40	Unit	Max timeout value CNT[6:0] = 0x7F	Unit
1/1	00	68.27		4.37	
1/2	01	136.53		8.74	
1/4	10	273.07	μs	17.48	ms
1/8	11	546.13		34.95	

^{(1).} Guaranteed by design, not tested in production.

4.25. Parameter condition

Unless otherwise specified, all values given for $V_{DD} = V_{DDA} = 3.3 \text{ V}$, $T_A = 25 \, ^{\circ}\text{C}$.



5. Package information

5.1. LQFP144 package outline dimensions

Figure 5-1. LQFP144 package outline

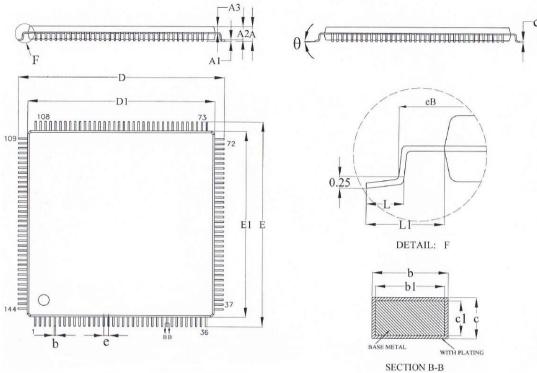


Table 5-1. LQFP144 package dimensions

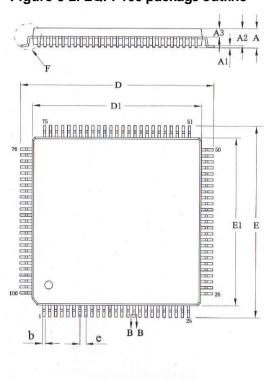
Symbol	Min	Тур	Max
А	_		1.60
A1	0.05		0.15
A2	1.35	1.40	1.45
А3	0.59	0.64	0.69
D	21.80	22.0	22.20
D1	19.90	20.0	20.10
E	21.80	22.0	22.20
E1	19.90	20.0	20.10
θ	0°	3.5°	7°
С	0.13		0.17
c1	0.12	0.13	0.14
L	0.45		0.75
L1	_	1.0 REF	_
b	0.18	_	0.26
b1	0.17	0.20	0.23
е	_	0.50 BSC	.



(Original dimensions are in millimeters)

5.2. LQFP100 package outline dimensions

Figure 5-2. LQFP100 package outline



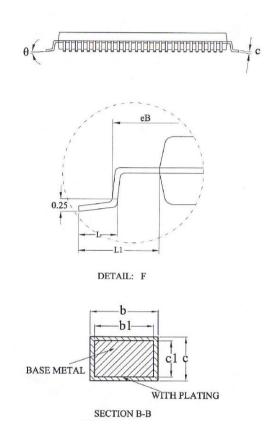


Table 5-2. LQFP100 package dimensions

Symbol	Min	Тур	Max
А	_	_	1.60
A1	0.05	_	0.15
A2	1.35	1.40	1.45
А3	0.59	0.64	0.69
D	15.80	16.0	16.20
D1	13.90	14.0	14.10
Е	15.80	16.0	16.20
E1	13.90	14.0	14.10
θ	0°	3.5°	7°
С	0.13	_	0.17
c1	0.12	0.13	0.14
L	0.45	0.6	0.75
L1	_	1.0 REF	
b	0.18	0.20	0.26
b1	0.17	0.20	0.23



GD32F307xx Datasheet

Symbol	Min	Тур	Max
eB	15.05	_	15.35
е	_	0.50 BSC	_

(Original dimensions are in millimeters)

SECTION B-B



5.3. LQFP64 package outline dimensions

Figure 5-3. LQFP64 package outline

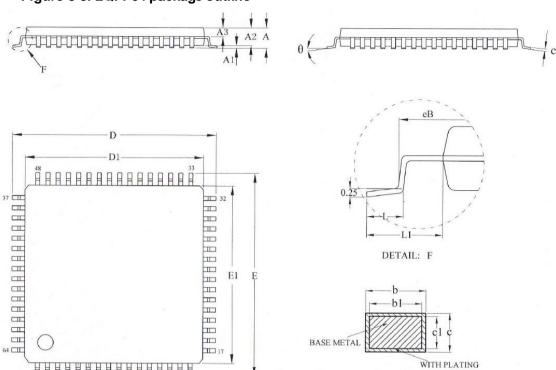


Table 5-3. LQFP64 package dimensions

Symbol	Min	Тур	Max
A	_		1.60
A1	0.05		0.15
A2	1.35	1.40	1.45
A3	0.59	0.64	0.69
D	11.80	12.00	12.20
D1	9.90	10.00	10.10
Е	11.80	12.00	12.20
E1	9.90	10.00	10.10
θ	0°	3.5°	7°
С	0.13		0.17
L	0.45	0.60	0.75
L1	_	1.00 REF	_
b	0.17	0.20	0.27
е	_	0.50 BSC	_
eB	11.25	_	11.45

(Original dimensions are in millimeters)



6. Ordering information

Table 6-1. Part ordering code for GD32F307xx devices

Ordering code	Flash (KB)	Package	Package type	Temperature operating range
GD32F307RCT6	256	LQFP64	Green	Industrial -40°C to +85°C
GD32F307RET6	512	LQFP64	Green	Industrial -40°C to +85°C
GD32F307RGT6	1024	LQFP64	Green	Industrial -40°C to +85°C
GD32F307VCT6	256	LQFP100	Green	Industrial -40°C to +85°C
GD32F307VET6	512	LQFP100	Green	Industrial -40°C to +85°C
GD32F307VGT6	1024	LQFP100	Green	Industrial -40°C to +85°C
GD32F307ZCT6	256	LQFP144	Green	Industrial -40°C to +85°C
GD32F307ZET6	512	LQFP144	Green	Industrial -40°C to +85°C
GD32F307ZGT6	1024	LQFP144	Green	Industrial -40°C to +85°C



7. Revision history

Table 7-1. Revision history

Revision No.	Description	Date
1.0	Initial Release	Mar.20, 2017
1.1	Repair history accumulation error	Jan.24, 2018
1.2	Repair history accumulation error	Dec.16, 2018
1.3	Add functional description of PD0 and PD1 to the packages below 100pin. Update electrical characteristics and package information.	Mar.6.2020
1.4	Correct the total number of ADC channel in features and peripheral list. refer to Table 2-1. GD32F307xx devices features and peripheral list	Jun.30, 2021



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